



CEIUPM

Centro de
Electrónica
Industrial

CAD tool to optimize the design of a PowerSoC converter: Powerswipe design case

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POLITÉCNICA

cei@upm.es

Introduction



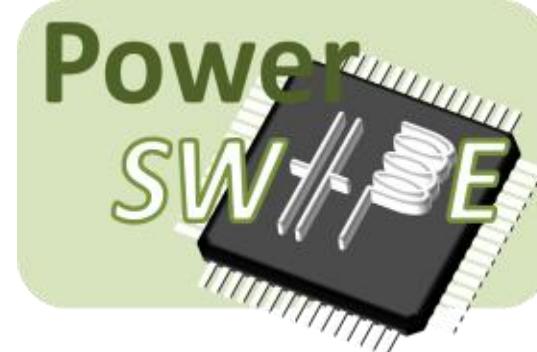
CAD Tool



Consortium Leader
Magnetics on Silicon



IC Design
200MHz LV PMIC



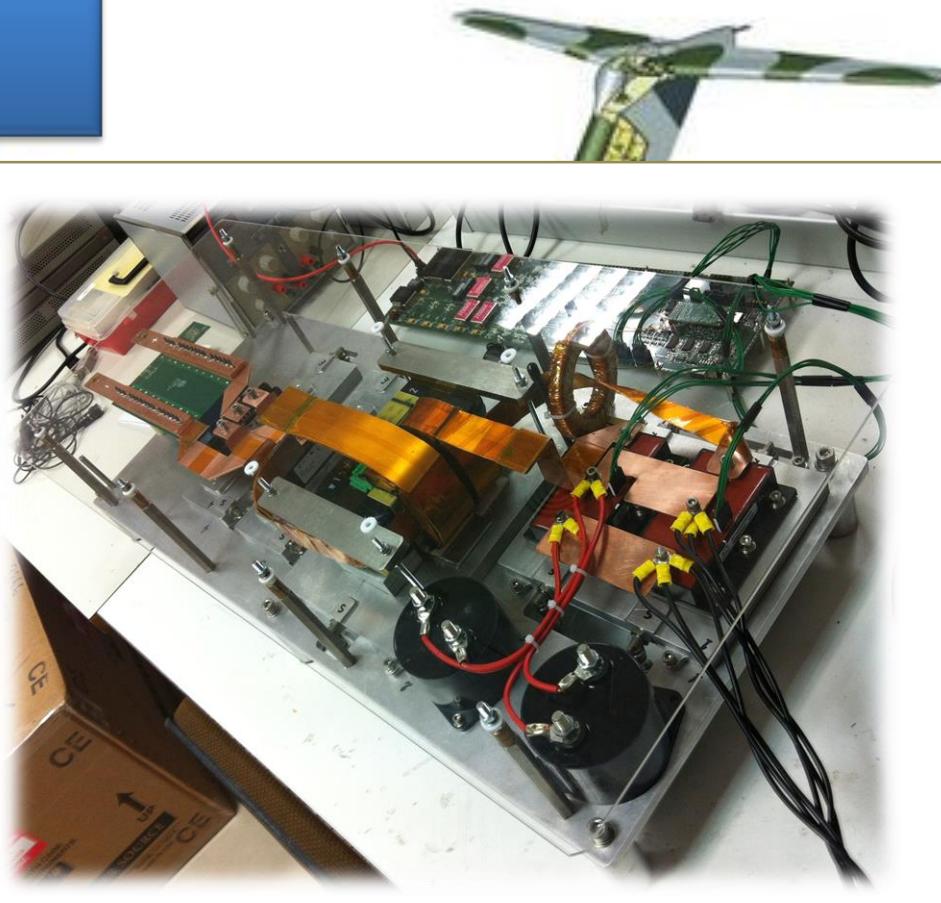
IFAT Villach
IC Design / Architecture
IFX Regensburg
Chip/Package Co-Design



Capacitors
Integration
Interposer

Gasoline engine ECU
System requirements

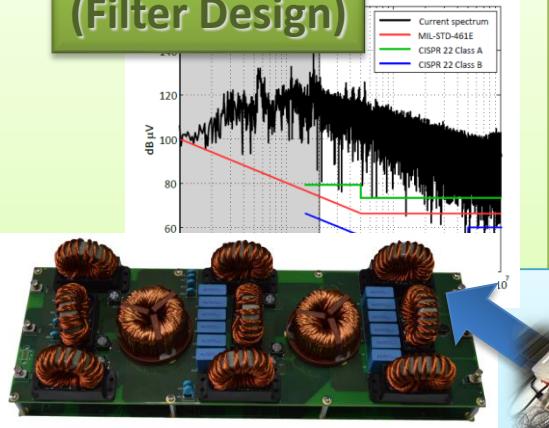
$10^6 \times$
factor



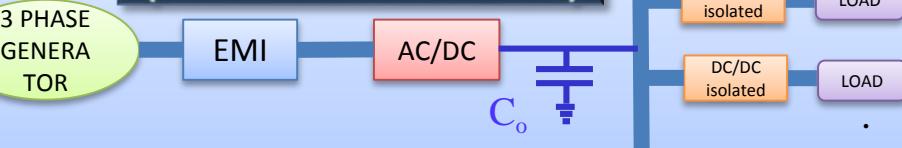
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Part of this knowledge is needed in PowerSoC

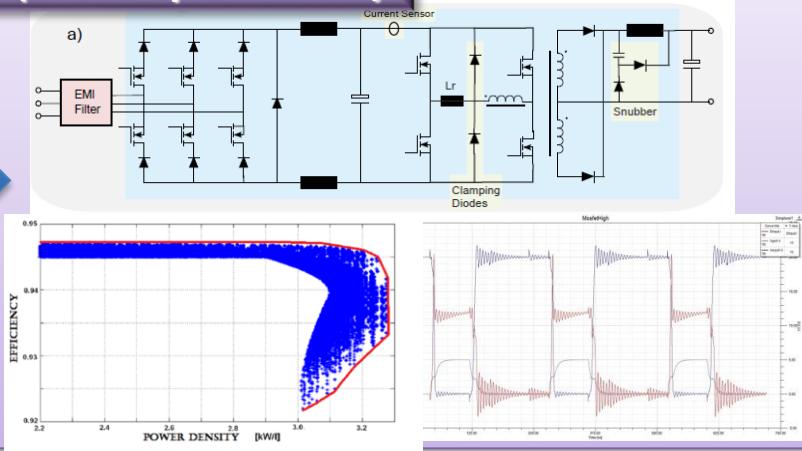
FDxprt (Filter Design)



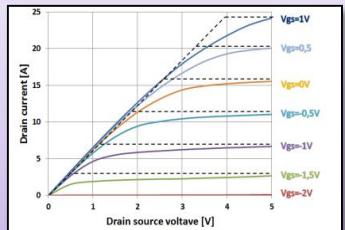
AGxprt (Architecture Generator)



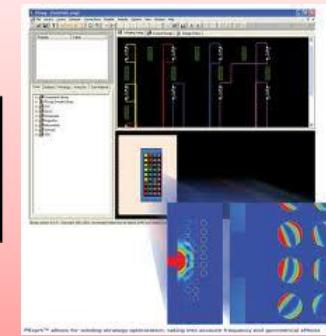
COxprt (circuit optimization)



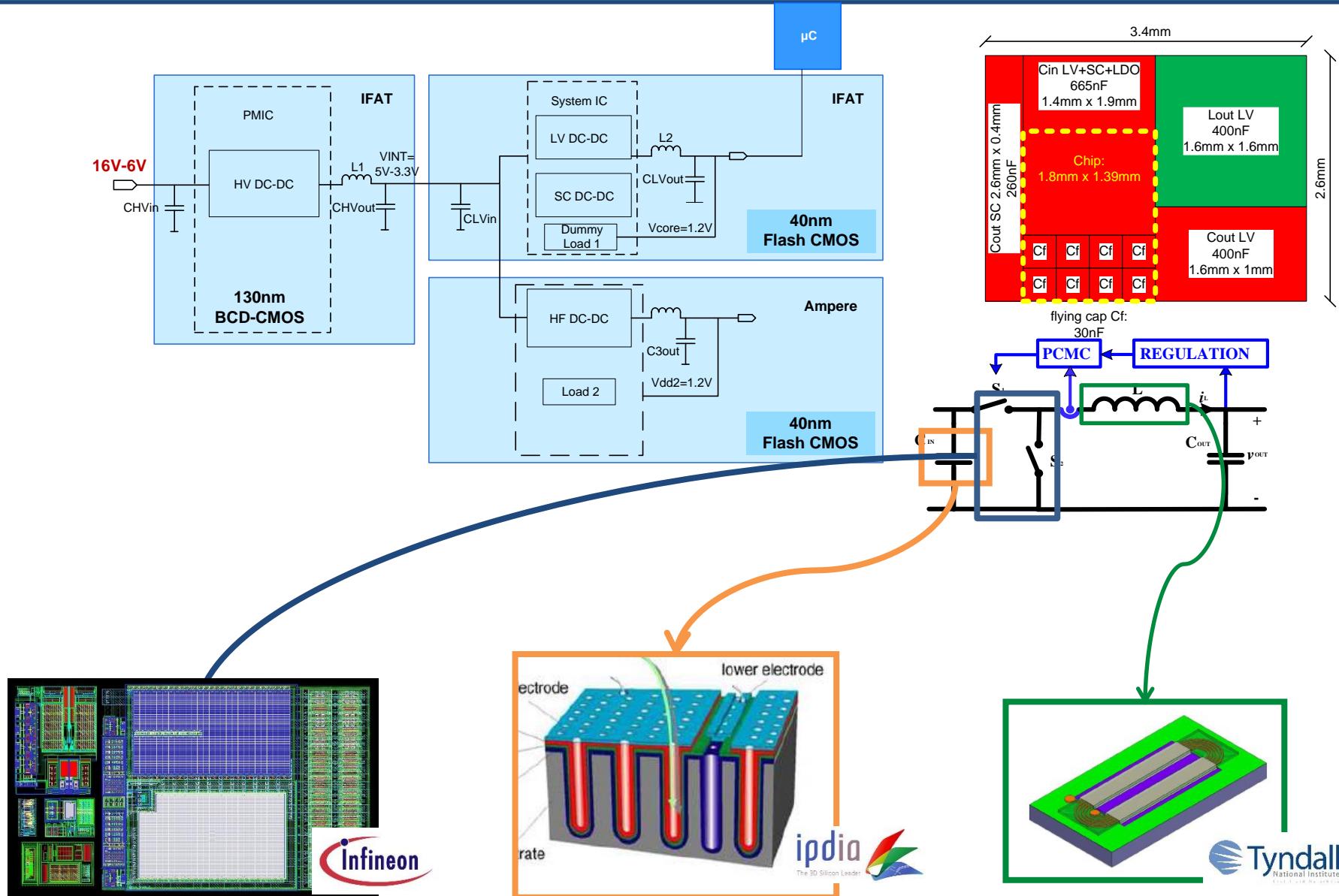
ChTool (Characterization Tool)



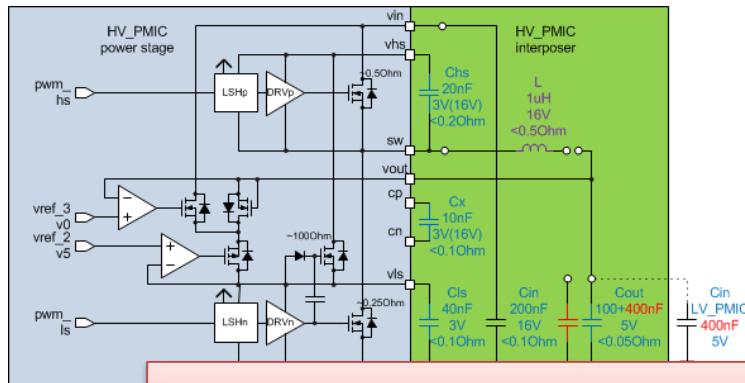
PExprt (Magnetic components)



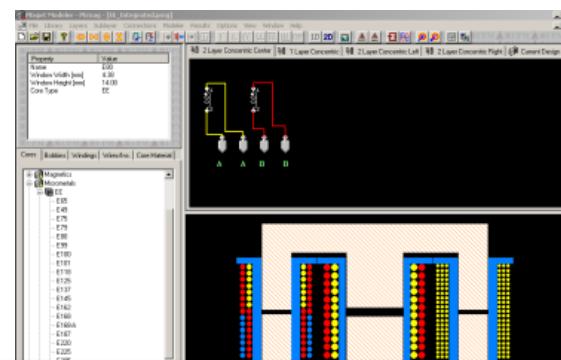
The need of an integrated multi-domain tool



Circuit Level Simulators



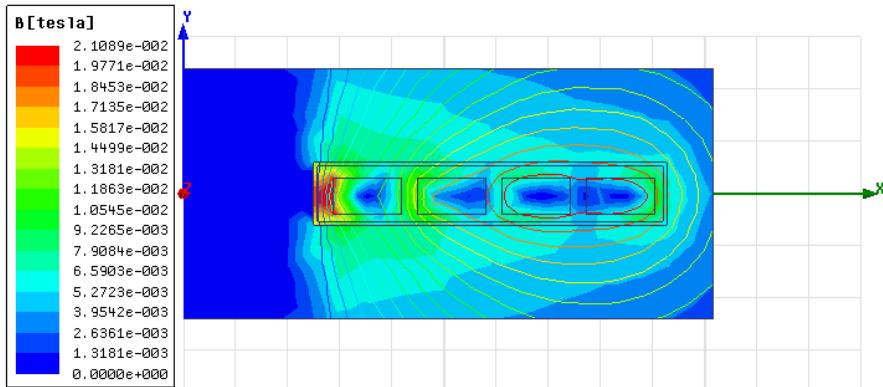
Magnetic Component Optimization Tools



PEXprt-Pemag
developed
by UPM

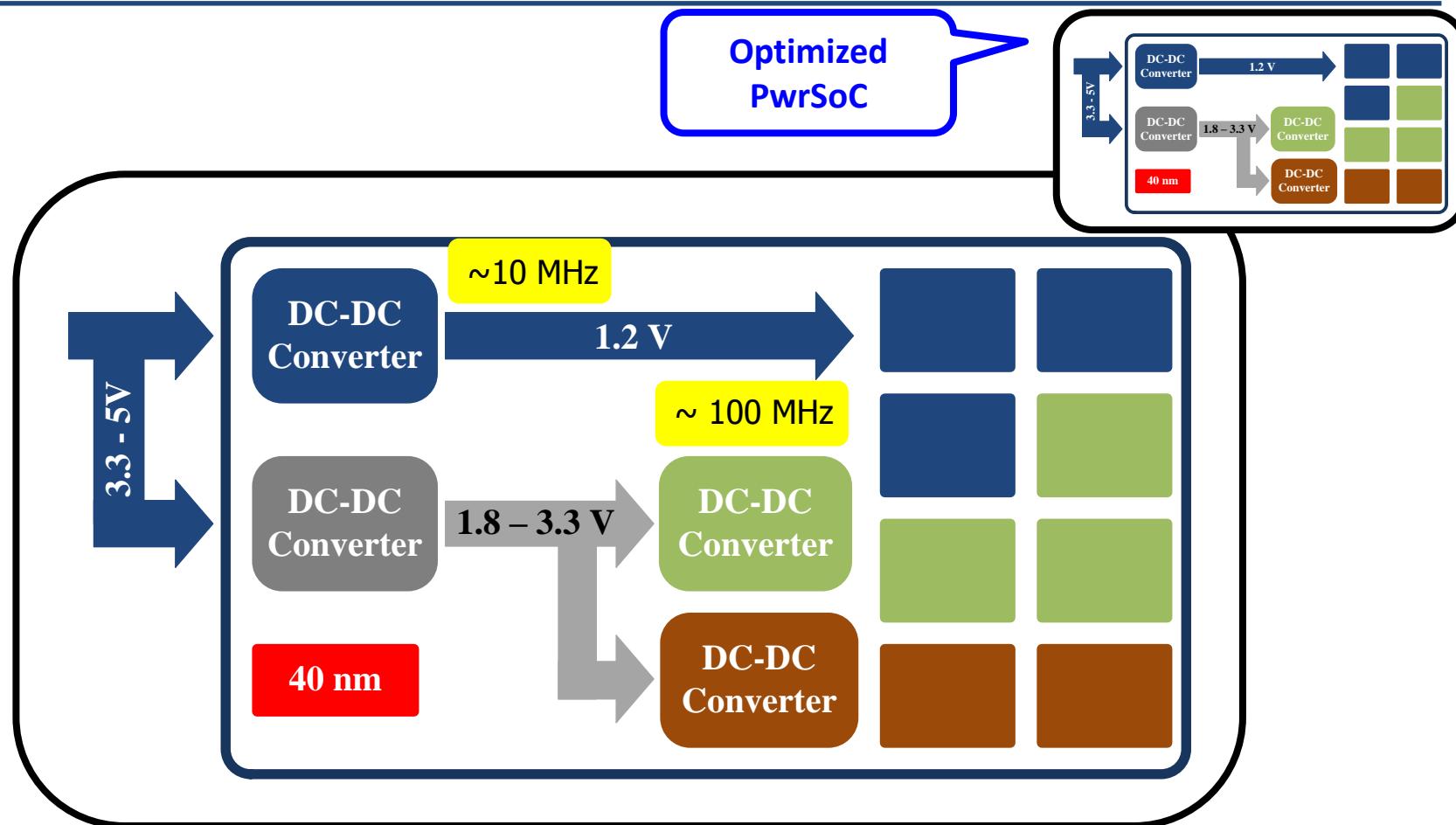
Lack of integrated design environment for Power Systems on Chip

Finite Element Analysis Tools

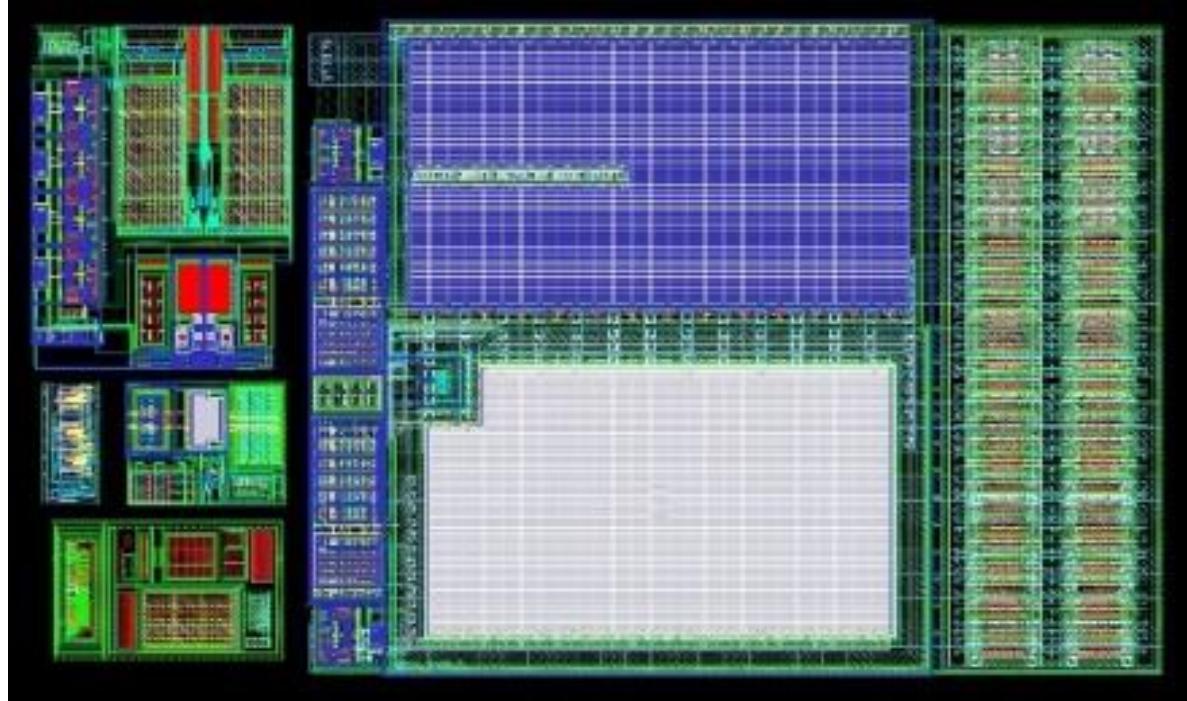
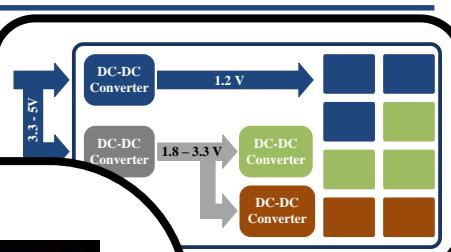


General Purpose Math Tools

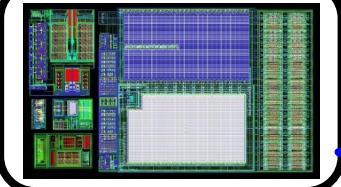


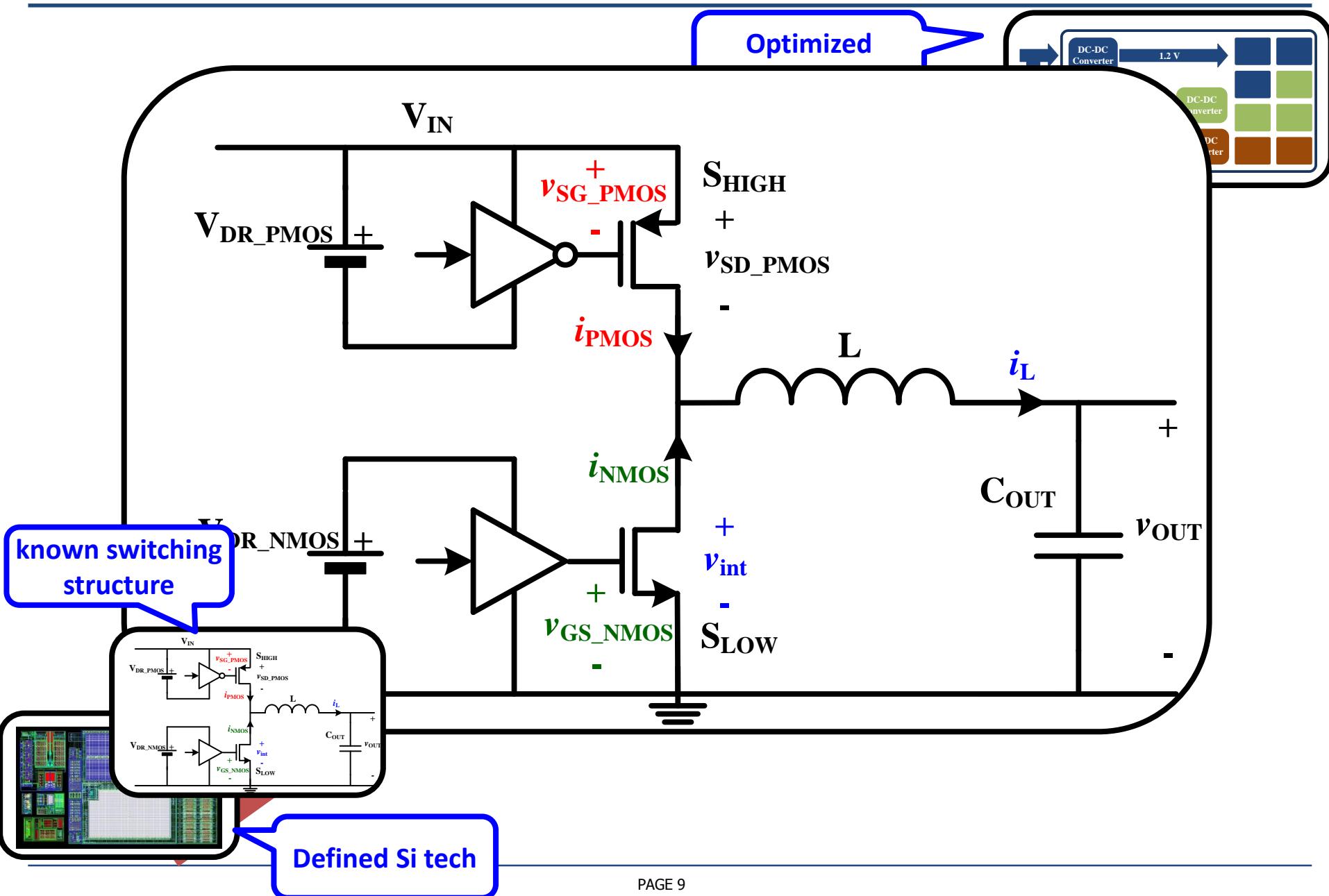


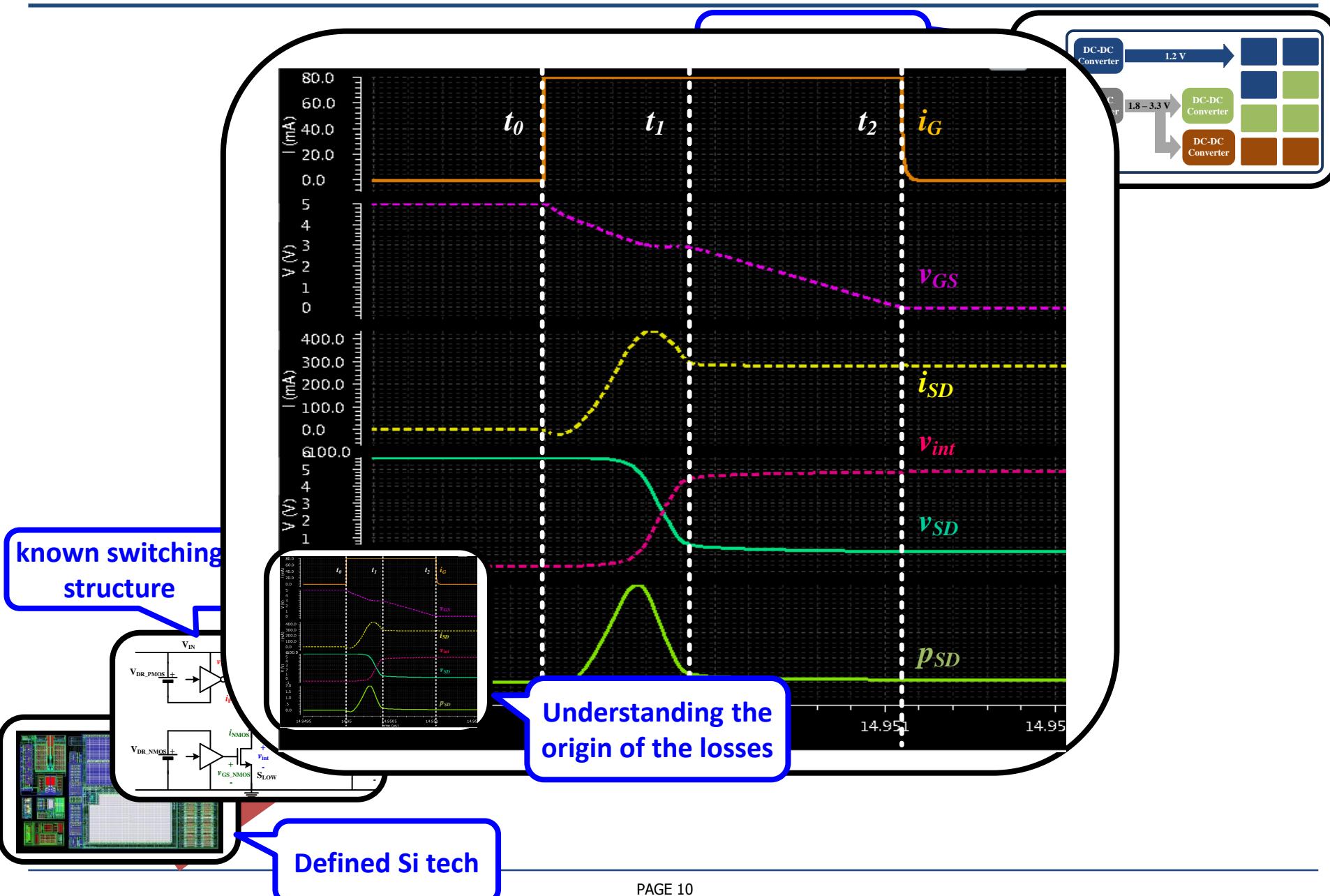
Optimized
PwrSoC

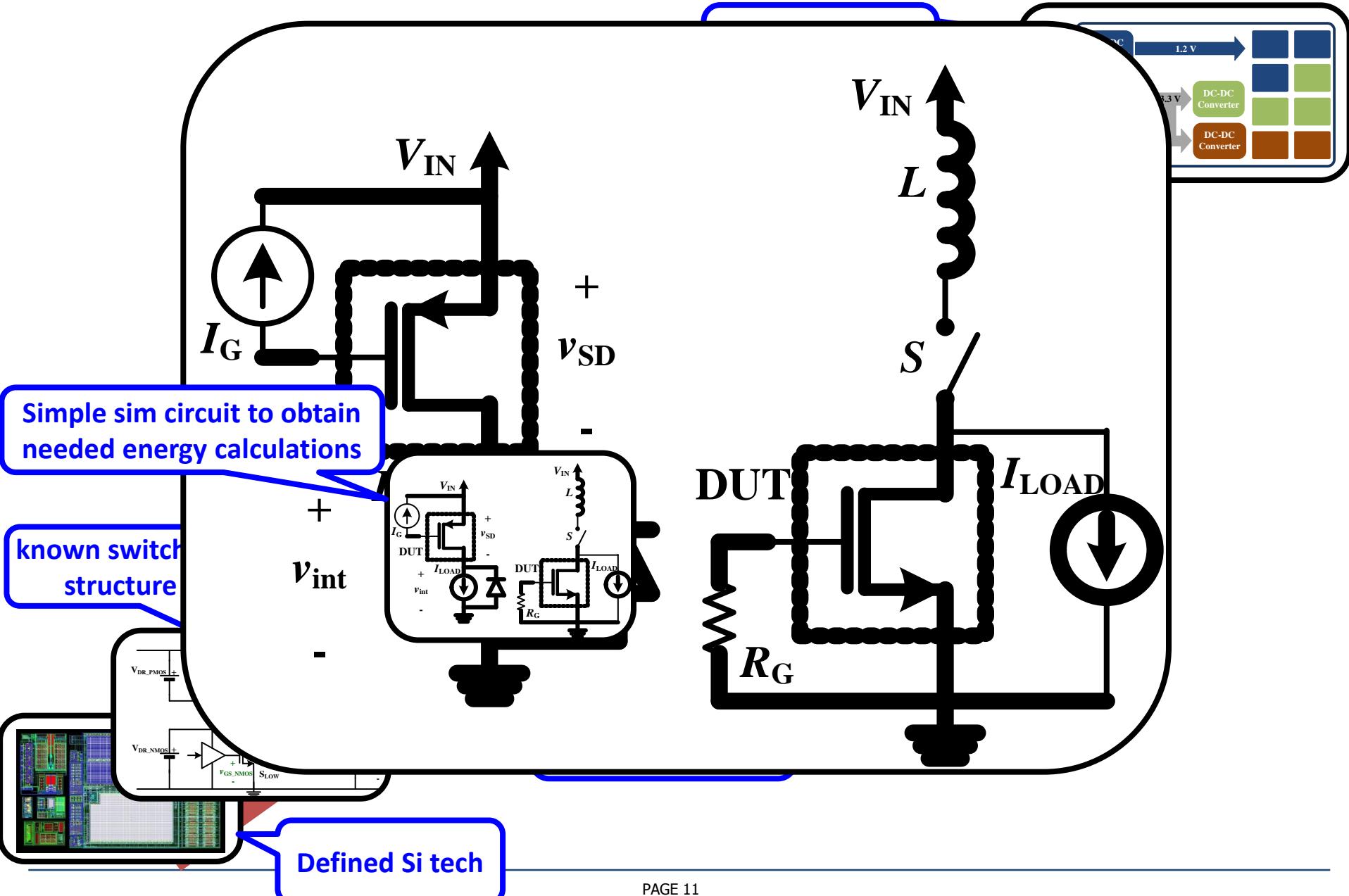


Defined Si tech





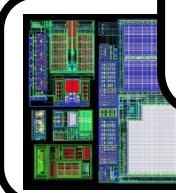




Pass
mode

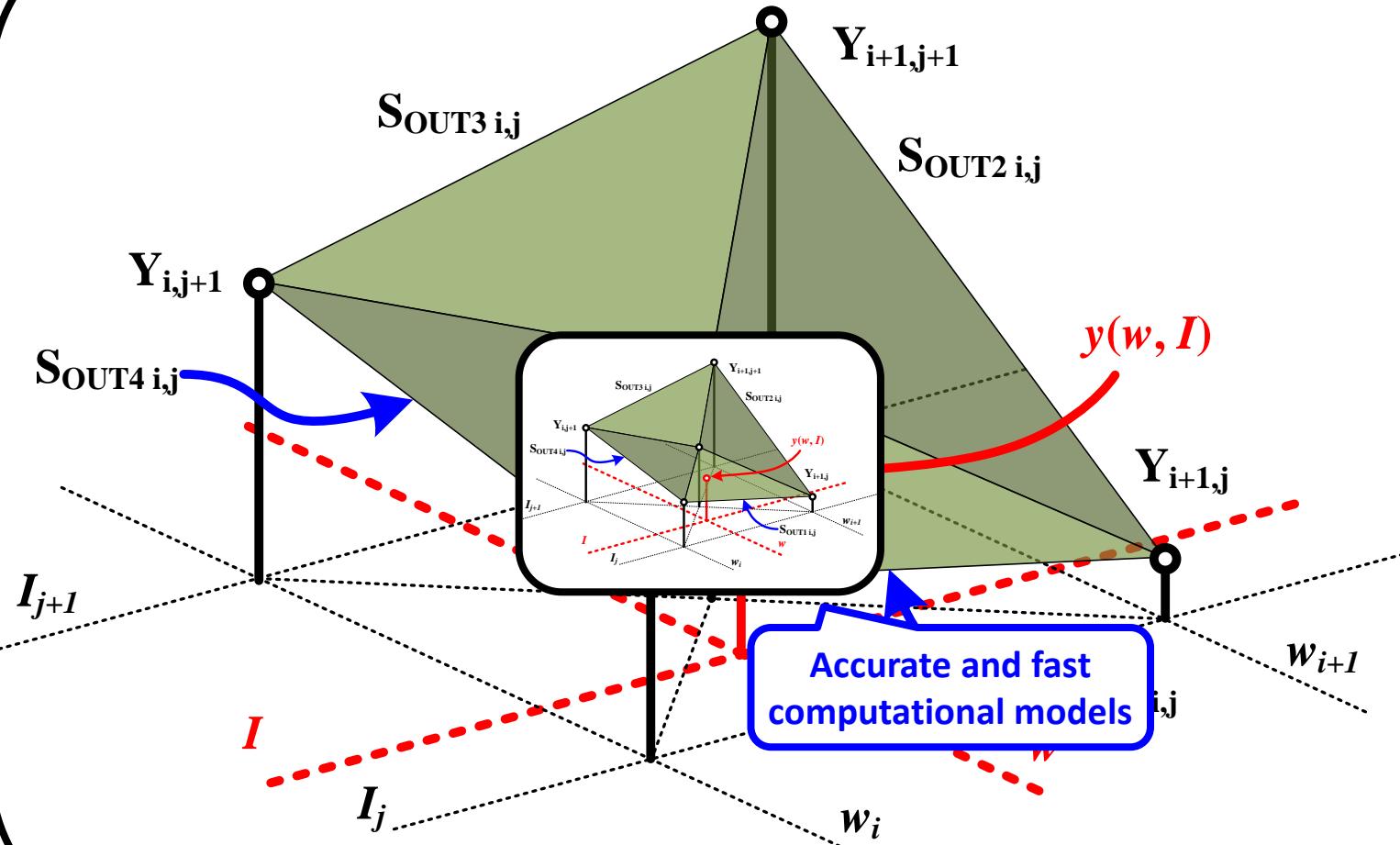
Simple
signals
needed

known
semicon-
ductor
struc-



Defined Si tech

Control



Optimized

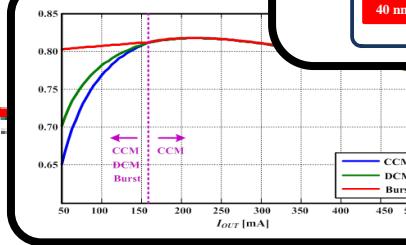
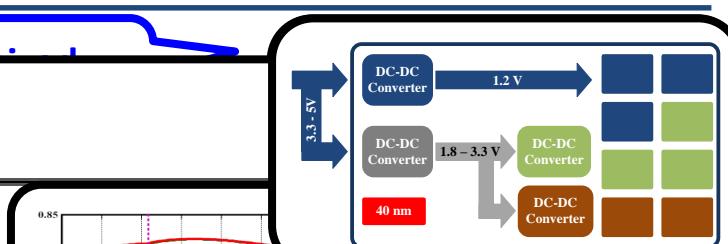
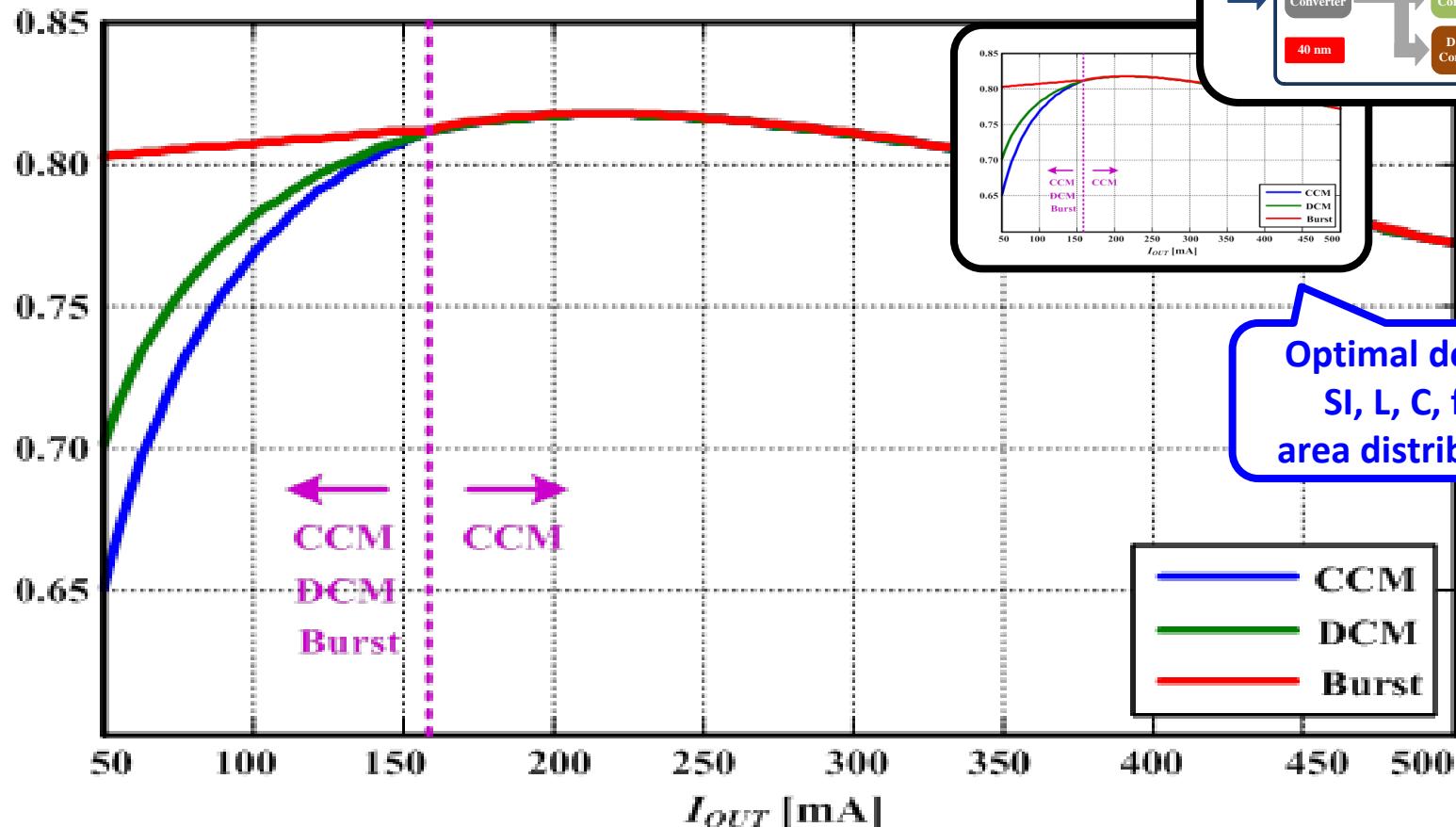
CAD optimization tool

Power Stage Specification

- Capacitors
 - Cout: 250 nF
 - Cin: 250 nF
 - Precision: 5 nF
 - Density: 220 nF/mm²
 - Area: 9 mm²
 - Vout pp: 60 mV
 - Vin pp: 60 mV
 - Rcin par: 10 mOhm
 - Lcin par: 100 pH
 - Rcout par: 10 mOhm
 - Lcout par: 100 pH
- MOSFETs
 - Hi side: Pmos
 - Wp: 8000 um
 - Wp min: 2000 um
 - Wp max: 30000 um
 - Vgs: 5.0 V
 - Ig max: 80 mA
 - Ron: 548.507 mOhm
 - LOW side: Nmos
 - Wh: 8000 um
 - Wh min: 2000 um
 - Wh max: 30000 um
 - Vgs: 5.0 V
 - Ig max: 80 mA
 - Ron: 171.658 mOhm
- Inductor
 - L: 150 nH
 - Lmax: 2000 nH
 - Precision: 1 nH
 - ILpp max: 500 mA
 - #Lamin.: 1
 - Area: 4 mm²
 - ILpp: 12 mA
 - R parz: 10 mOhm
 - L parz: 100 pH
- Regulator Constraints
 - PM: 60 deg
 - BWmin: 0 MHz
 - BW: 5 MHz
- Load Design Control
 - Single Buck VMC: CCM solution
 - Select Optimized Values:
 - Cin/Cout
 - Lout
 - fsw
 - wp
 - wn
 - Area
 - Load Design
- Target Efficiency
 - ni @ lout typical: 90 %
 - ni @ lout maximal: 85 %
 - ni @ lout minimal: 75 %
- Load Steps
 - Dlout: 50, 300 mA
 - Set. Time: 2, 20000 ns
- Input Voltage Steps
 - DVin: 250 mV
 - Set. Time: 0 ns
- Control of the system
 - Voltage Mode Control
 - Peak Current Mode Control

Defined Si tech

Control



Optimal design:
SI, L, C, f_{SW} ,
area distribution

- CCM
- DCM
- Burst

Sinc
ne

kno

Defined Si tech

Control

Passives models

Simple sim circuit to obtain
needed energy calculations

known switching
structure

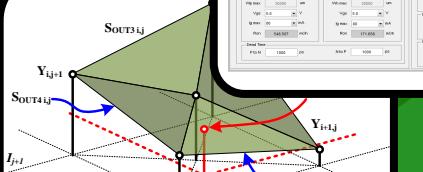
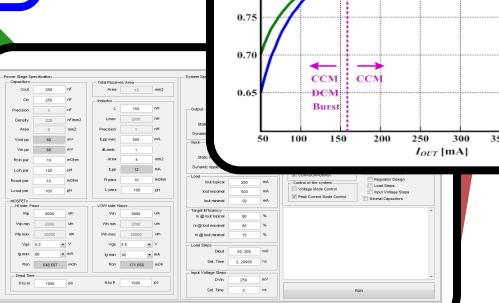
Defined Si tech

CAD optimization tool

Optimized
PwrSoC

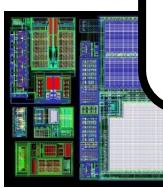
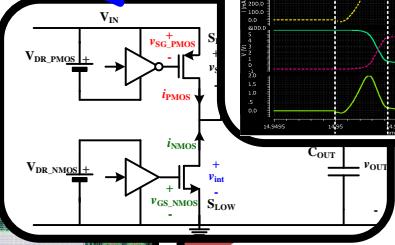
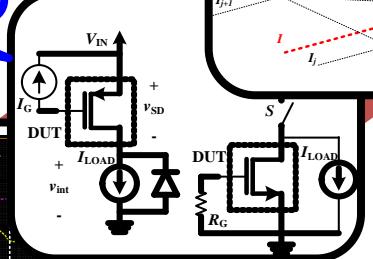
Optimal design:
SI, L, C, f_{SW} ,
area distribution

Control

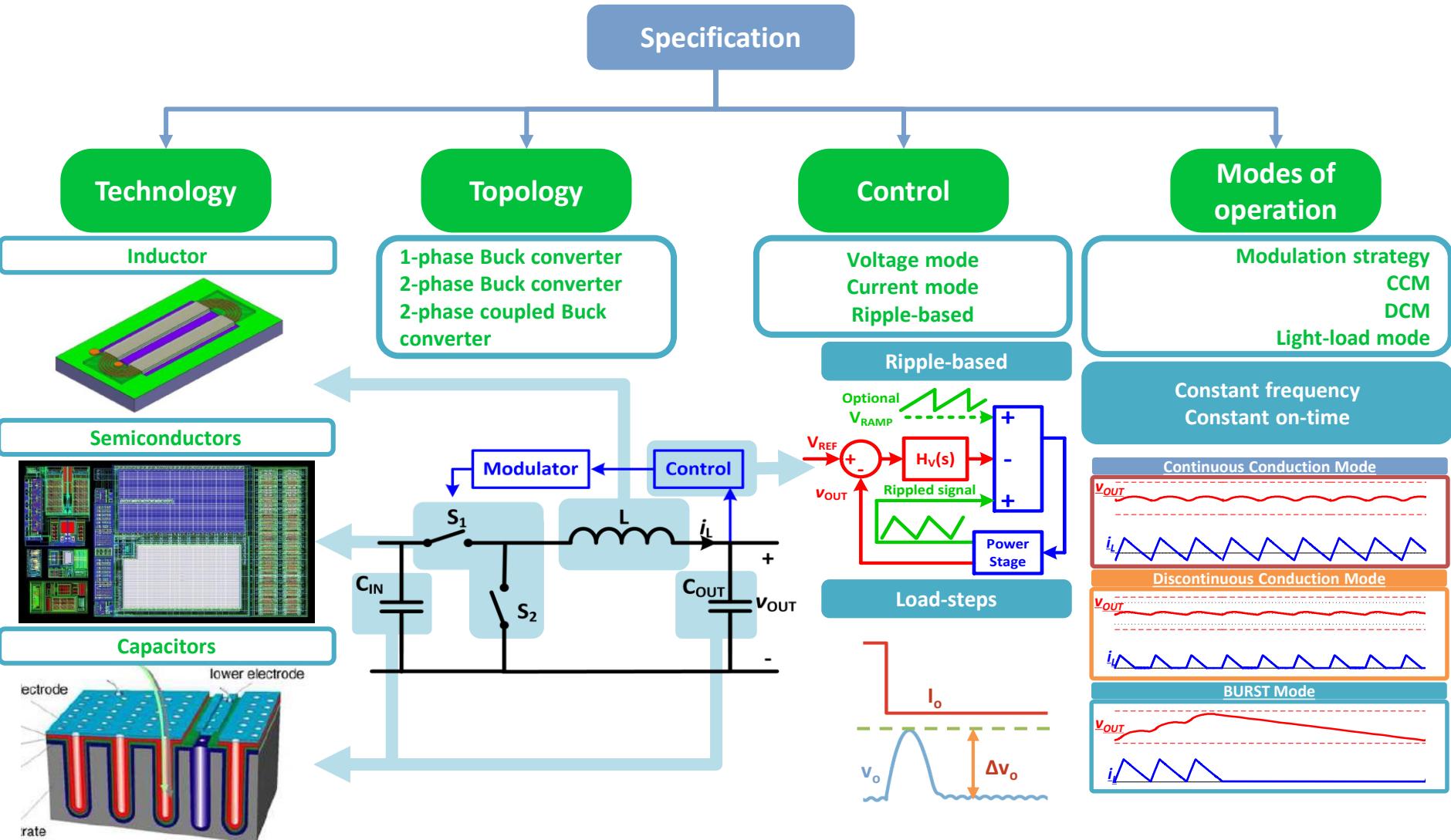


Accurate and fast
computational models

Understanding the
origin of the losses



PowerSoC “design flow”: Designer options



PowerSoC “design flow”: Designer options

Technology

Power Stage Specification

Capacitors	Cout: 250 nF	Total Passives Area	Area: 13 mm ²
Precision	Cin: 250 nF	Inductor	L: 150 nH
Density	5 nF/mm ²	Lmax: 2000 nH	Precision: 1 nH
Area	220 nF/mm ²	ILpp max: 500 mA	#Lamin.: 1
Vout pp	9 mm ²	Area: 4 mm ²	ILpp: 12 mA
Vin pp	60 mV	R parz: 10 mOhm	R parz: 100 pH
Ron par	60 mV	L parz: 100 pH	
Lcin par	10 mOhm		
Rcout par	100 pH		
Lcout par	100 pH		

MOSFETs

Hi side: Pmos	V _{wp} : 8000 um	LOVV side: Nmos	V _{wn} : 8000 um
V _{wp} min	2000 um	V _{wn} min	2000 um
V _{wp} max	30000 um	V _{wn} max	30000 um
V _{gs}	5.0 V	V _{gs}	5.0 V
I _g max	80 mA	I _g max	80 mA
R _{on}	548.507 mOhm	R _{on}	171.658 mOhm
Dead Time	P to N: 1000 ps	N to P: 1000 ps	

Topology

Specification

System Specification

f _{sw}	20 MHz
f _{sw} min	1 MHz
f _{sw} max	30 MHz
Output	V _{out} : 1.2 V
Static ripple pp	5 %
Dynamic ripple pp	12 %
Input	V _{in} : 5 V
Static ripple pp	5 %
Dynamic ripple pp	5 %
Load	I _{out} typical: 280 mA
I _{out} maximal	500 mA
I _{out} minimal	50 mA

Regulator Constrains

PM	60 deg
BW _{min}	0 MHz
BW	5 MHz
BW _{max}	5 MHz

Load Design Control

Single Buck VMC: CCM solution		
Select Optimized Values:		
<input checked="" type="checkbox"/> Cin/Cout	<input checked="" type="checkbox"/> Lout	<input checked="" type="checkbox"/> f _{sw}
<input checked="" type="checkbox"/> wp	<input checked="" type="checkbox"/> wn	<input checked="" type="checkbox"/> Area
Load Design		

Control

Control

Topology	<input checked="" type="checkbox"/> Single Phase Buck	<input type="checkbox"/> Two Phase Buck	<input type="checkbox"/> Coupled Two Phase Buck
L mag	700 nH		
Optimization	<input type="checkbox"/> Cin/Cout	<input type="checkbox"/> Lout	<input type="checkbox"/> f _{sw}
Analysis	<input checked="" type="checkbox"/> Static Behaviour	<input type="checkbox"/> @ I _{out} typ	<input type="checkbox"/> @ I _{out} max
Mode of Operation	<input type="checkbox"/> CCM only	<input type="checkbox"/> I _{out} Sweep	<input type="checkbox"/> @ I _{out} min
<input checked="" type="checkbox"/> CCM+DCM+BURST			
Control of the system	<input type="checkbox"/> Regulator Design	<input type="checkbox"/> Load Steps	<input type="checkbox"/> Input Voltage Steps
	<input type="checkbox"/> Voltage Mode Control	<input checked="" type="checkbox"/> Peak Current Mode Control	<input type="checkbox"/> Minimal Capacitors

Target Efficiency

n _i @ I _{out} typical	90 %
n _i @ I _{out} maximal	85 %
n _i @ I _{out} minimal	75 %

Load Steps

D _{out}	50, 300 mA
Set. Time	2, 20000 ns

Input Voltage Steps

D _{in}	250 mV
Set. Time	0 ns

RUN

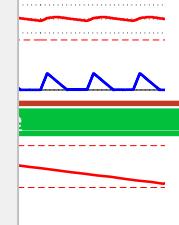
Modes of operation

Conduction strategy
Cond. Mode
Cond. Mode
t-load mode

Efficiency
time

on Mode

on Mode



Power Stage Specification

Capacitors	Cout	250	nF
	Cin	250	nF
Precision		5	nF
Density		220	nF/mm ²
Area		9	mm ²
Vout pp		60	mV
Vin pp		60	mV
Rcin par		10	mOhm
Lcin par		100	pH
Rcout par		10	mOhm
Lcout par		100	pH

MOSFETs

Hi side: Pmos	V _{tp}	8000	um
	V _{tp} min	2000	um
	V _{tp} max	30000	um
	V _{gs}	5.0	V
	I _g max	80	mA
	R _{on}	548.507	mOh
Low side: Nmos	V _{tn}	8000	um
	V _{tn} min	2000	um
	V _{tn} max	30000	um
	V _{gs}	5.0	V
	I _g max	80	mA
	R _{on}	171.658	mOh

Dead Time

P to N	1000	ps
N to P	1000	ps

Total Passives Area

Area	13	mm ²
------	----	-----------------

Inductor

L	150	nH
Lmax	2000	nH

Precision

Precision	1	nH
-----------	---	----

ILpp max

ILpp max	500	mA
----------	-----	----

#Lamin.

#Lamin.	1	
---------	---	--

Area

Area	4	mm ²
------	---	-----------------

ILpp

ILpp	12	mA
------	----	----

Rparz

Rparz	10	mOhm
-------	----	------

Lparz

Lparz	100	pH
-------	-----	----

System Specification

fsw	20	MHz	
fsw min	1	MHz	
fsw max	30	MHz	
Output	Vout	1.2	V
	Static ripple pp	5	%
	Dynamic ripple pp	12	%
Input	Vin	5	V
	Static ripple pp	5	%
	Dynamic ripple pp	5	%

Target Efficiency

ni @ lout typical	90	%
ni @ lout maximal	85	%
ni @ lout minimal	75	%

Load Steps

Dlout	50, 300	mA
Set. Time	2, 20000	ns

Input Voltage Steps

DVin	250	mV
Set. Time	0	ns

Regulator Constrains

PM	60	deg
BVmmin	0	MHz
BVm	5	MHz
BVmmax	5	MHz

Load Design Control

Single Buck VMC: CCM solution

Select Optimized Values:

- Cin/Cout
- Lout
- fsw
- wp
- wn
- Area

Control

Topology

- Single Phase Buck
- Two Phase Buck
- Coupled Two Phase Buck
- L mag 700 nH

Analysis

- Optimization
- Cin/Cout
- Lout
- fsw
- wp
- wn
- Area

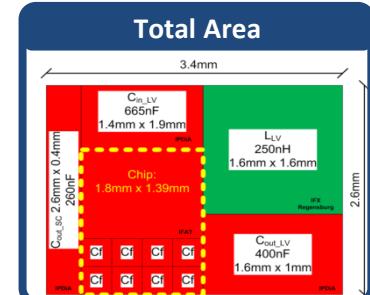
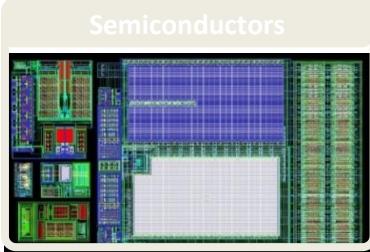
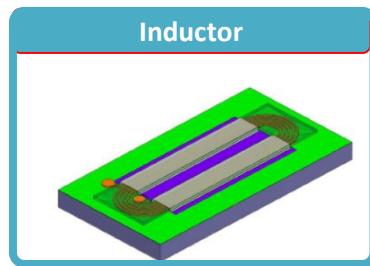
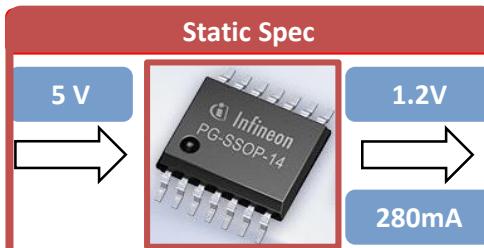
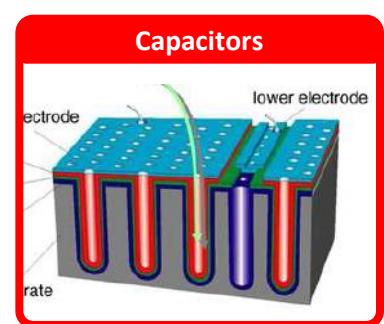
Mode of Operation

- CCM only
- CCM+DCM+BURST

Control of the system

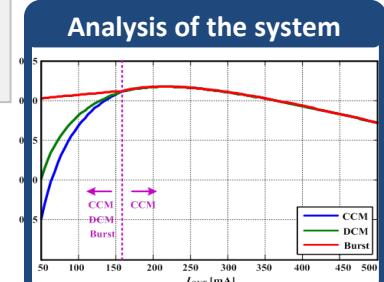
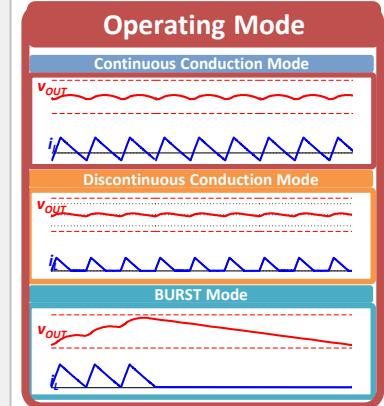
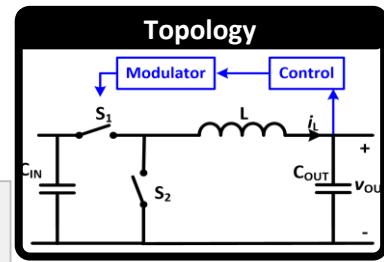
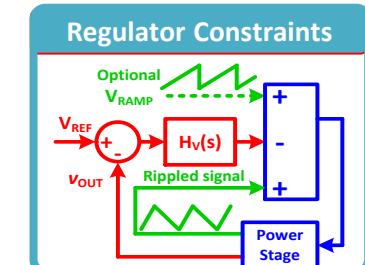
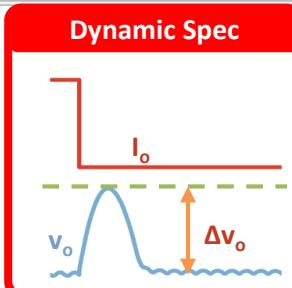
- Voltage Mode Control
- Load Steps
- Input Voltage Steps
- Peak Current Mode Control
- Minimal Capacitors

RUN



Two Stage Specification

Capacitors	C_{out} : 250 nF C_{in} : 250 nF Precision: 5 nF Density: 220 nF/mm ² Area: 9 mm ² Vout pp: 60 mV Vin pp: 60 mV Ron par: 10 mOhm Lout par: 100 pH Rout par: 10 mOhm Lout par: 100 pH	Total Passives Area Area: 13 mm ²	L: 150 nH Lmax: 2000 nH Precision: 1 nH ILpp max: 500 mA #Lamin.: 1 Area: 4 mm ² ILpp: 12 mA Rparz: 10 mOhm Lparz: 100 pH	System Specification fsw: 20 MHz fsw min: 1 MHz fsw max: 30 MHz Output: Vout: 1.2 V Static ripple pp: 5 % Dynamic ripple pp: 12 % Input: Vin: 5 V Static ripple pp: 5 % Dynamic ripple pp: 5 % Load: Iout typical: 280 mA Iout maximal: 500 mA Iout minimal: 50 mA	Regulator Constraints PM: 60 deg Bfmin: 0 MHz Bf: 5 MHz Bfmax: 5 MHz Control Topology: Single Phase Buck Two Phase Buck Coupled Two Phase Buck Input: Vip: 8000 um Vip min: 2000 um Vip max: 30000 um Vgs: 5.0 V Ig max: 80 mA Ron: 548.507 mOhm Dead Time: P to N: 1000 ps N to P: 1000 ps Vth min: 2000 um Vth max: 30000 um Vgs: 5.0 V Ig max: 80 mA Ron: 171.658 mOhm Target Efficiency ni @ Iout typical: 90 % ni @ Iout maximal: 85 % ni @ Iout minimal: 75 % Dout: 50, 300 mA Set. Time: 2, 20000 ns Input Voltage Steps DVin: 250 mV Set. Time: 0 ns
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Capacitors

Static Spec

Regulator Constraints

Load Design

Topology

Inductor

Semiconductors

Total Area

Dynamic Spec

Optimization

Cin/Cout

Lout

fsw

wp

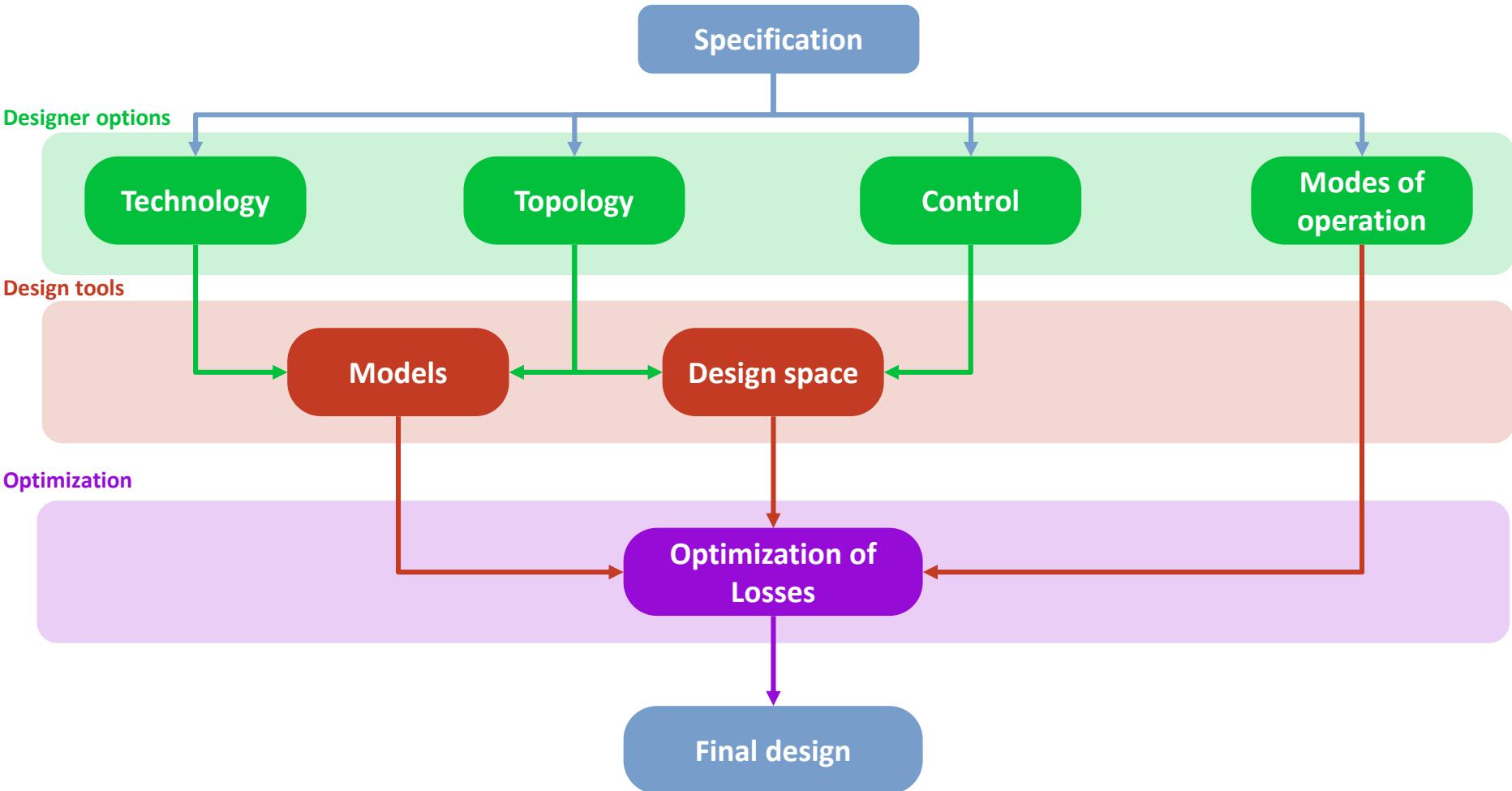
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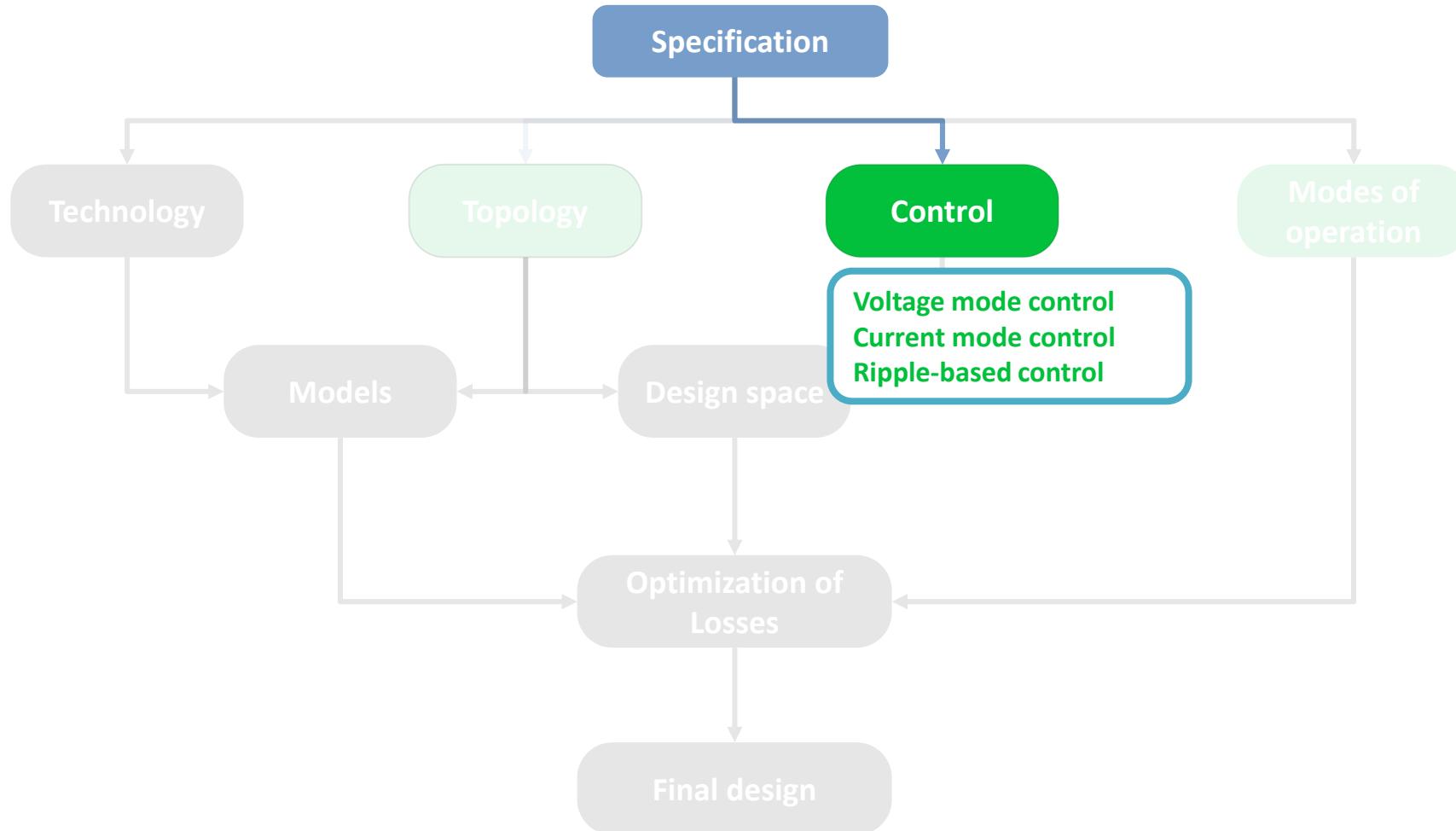
Area

Operating Mode

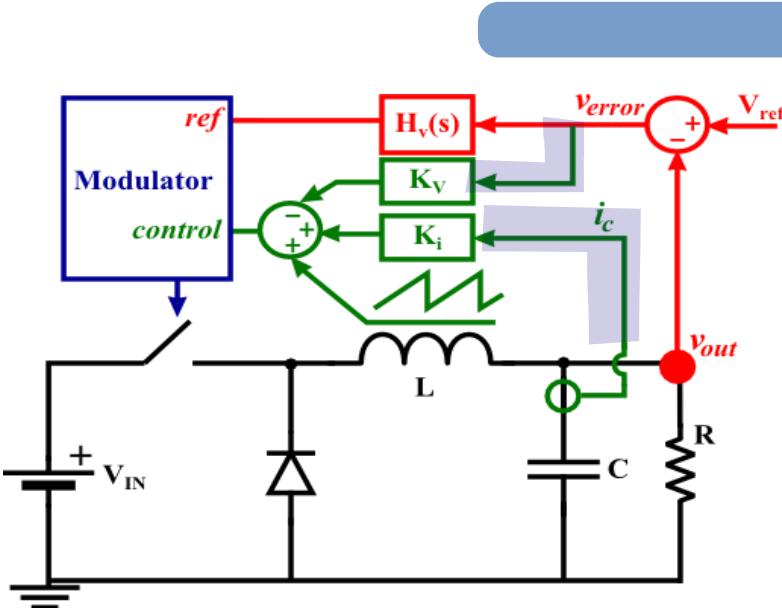
- continuous Conduction Mode
- continuous Conduction Mode
- BURST Mode

Analysis of the system

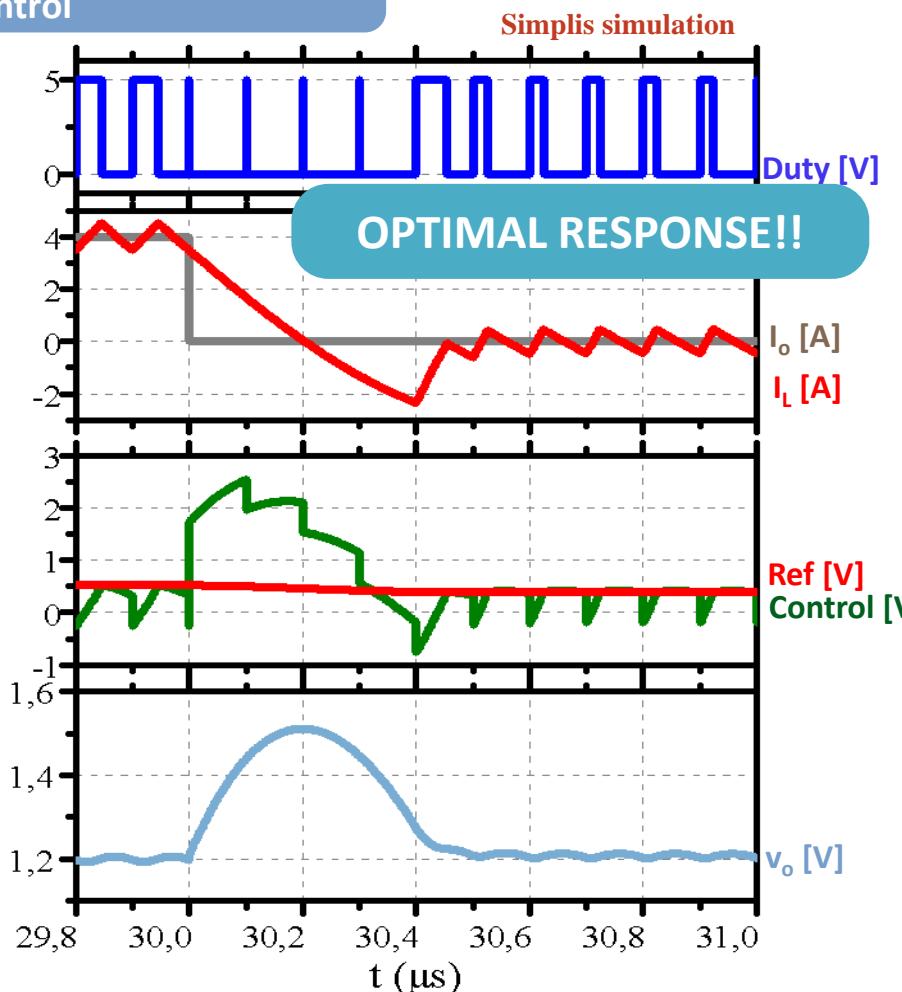




Ripple based Control



V^2I_c control



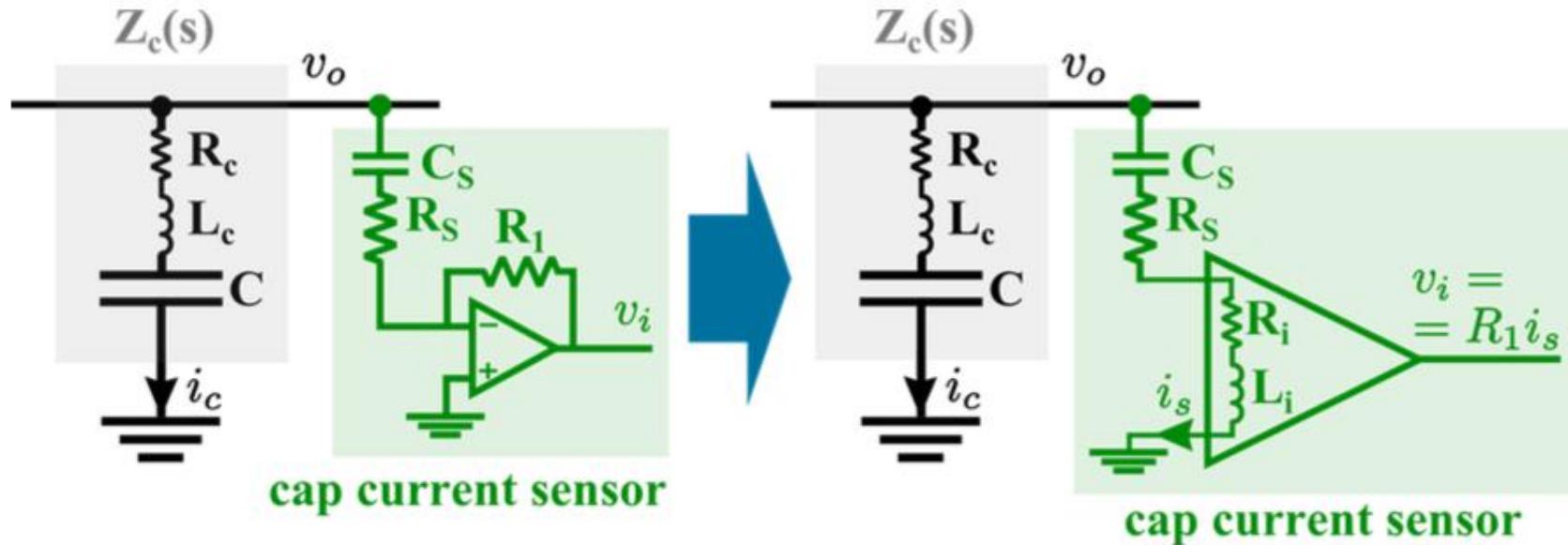
Very fast even with low ESR caps

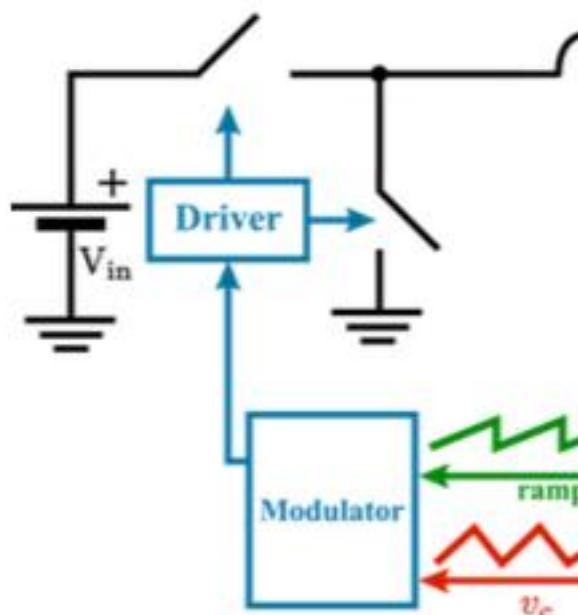
- Feedforward of:
- Output current
 - Voltage reference

✗ Complex analysis, SIMPLE implementation

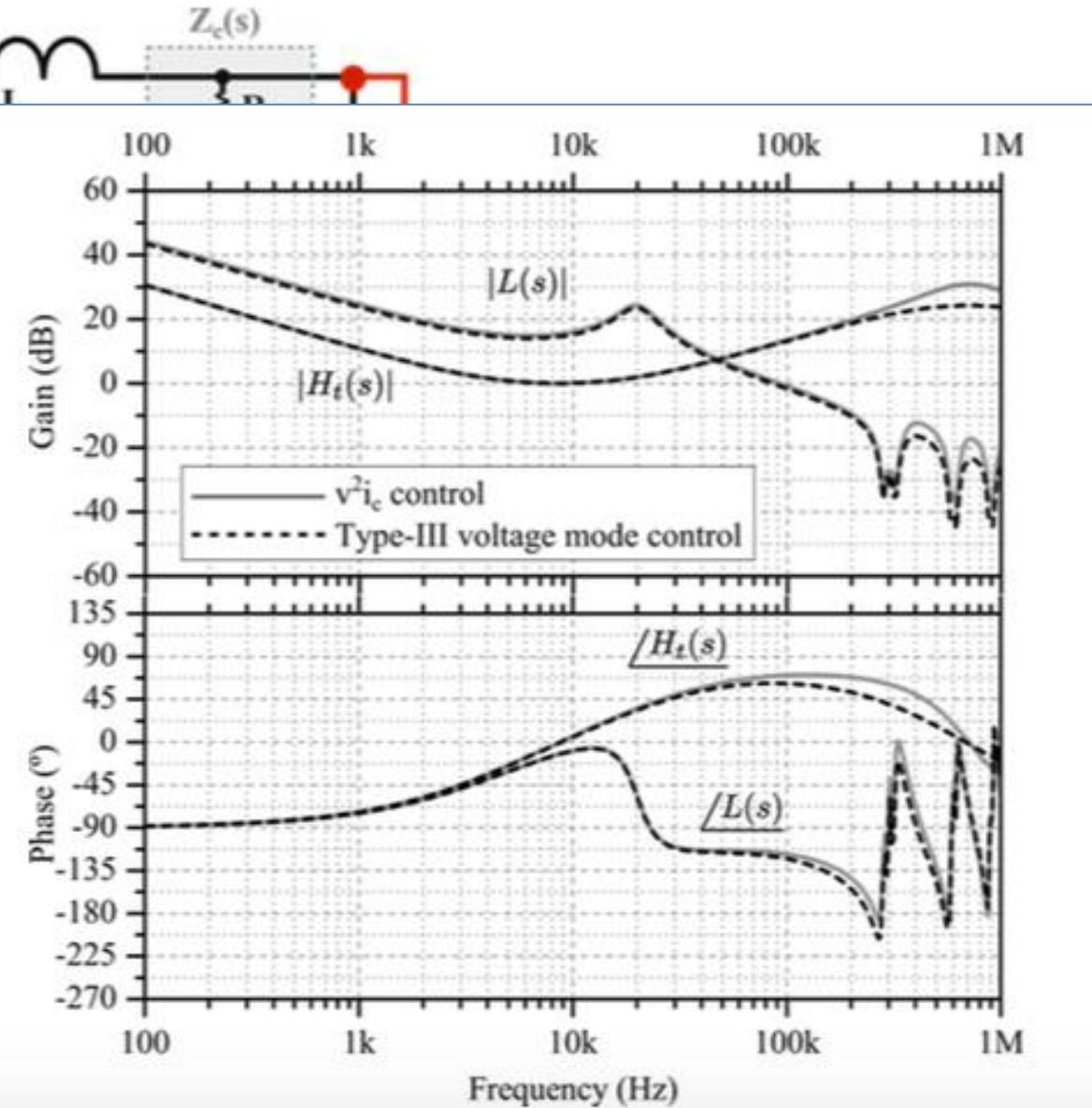


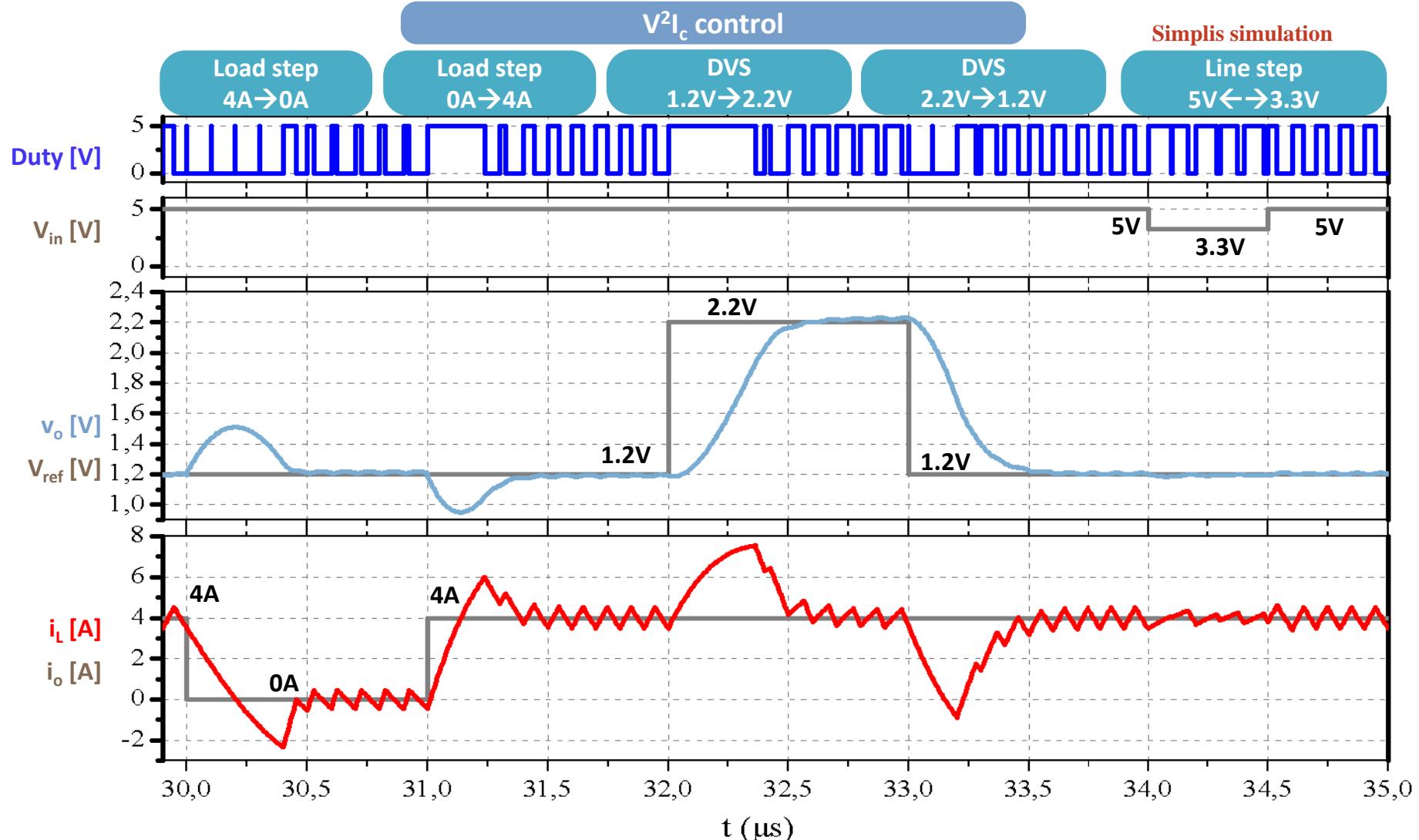
Del Viejo, M.; Alou, P.; Oliver, J.A.; Garcia, O.; Cobos, J.A., "V²I_c control: A novel control technique with very fast response under load and voltage steps," *Applied Power Electronics Conference and Exposition (APEC)*, 2011 Twenty-Sixth Annual IEEE , vol., no., pp.231,237, 6-11 March 2011

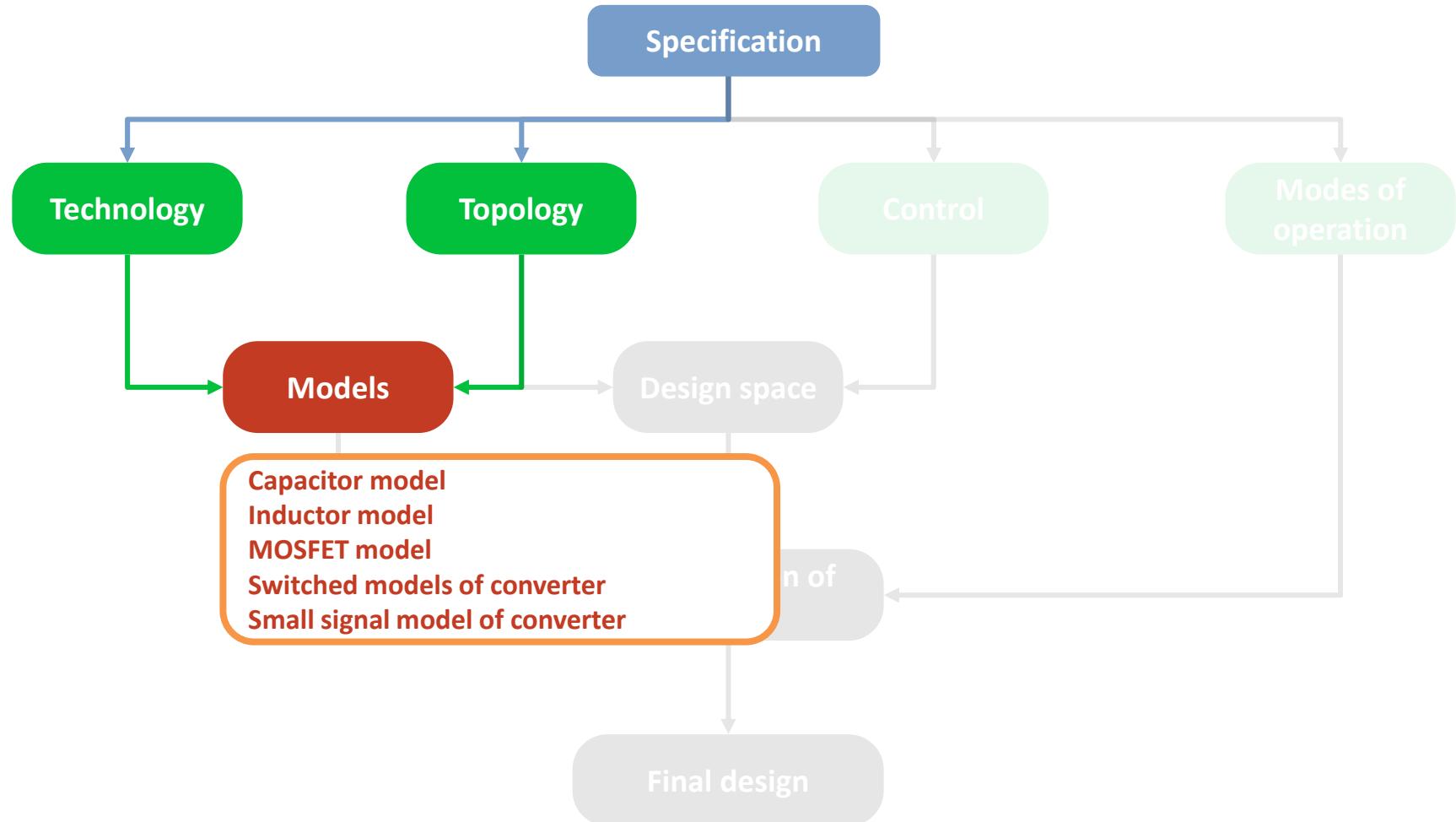


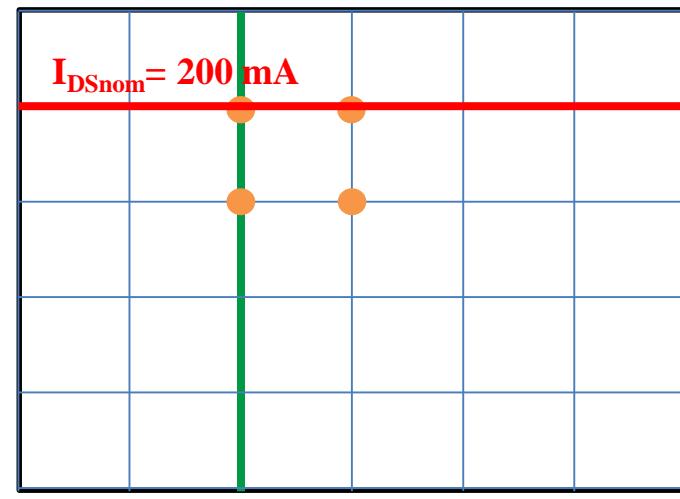
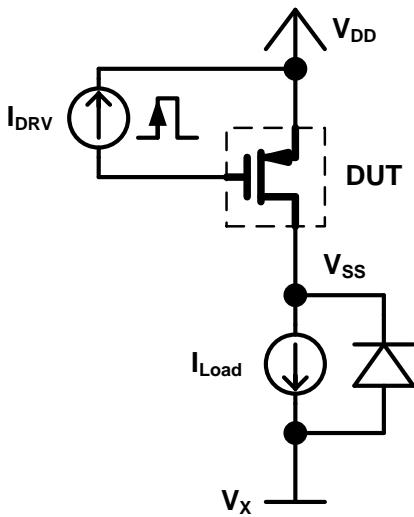


$$H_t(s) = A_0/s + K_v + K_i$$



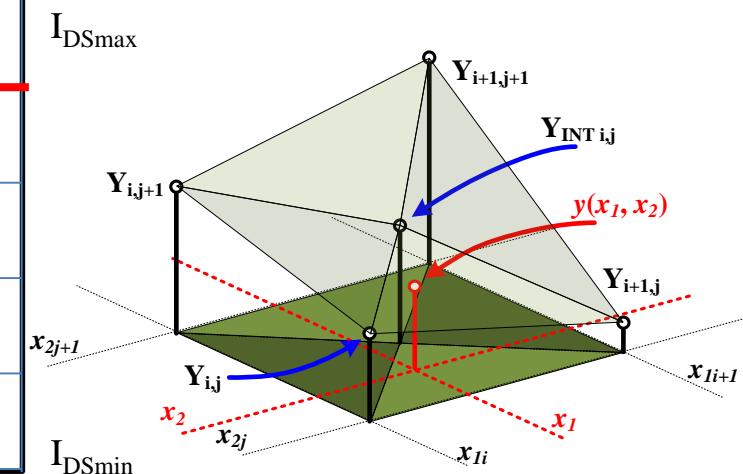






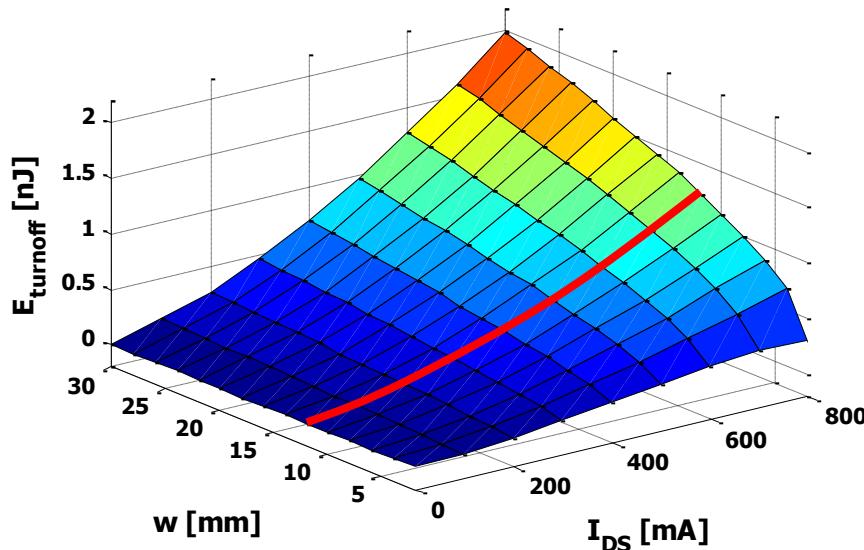
$$\begin{aligned} w_{Pnom} &= 10.6 \text{ mm} \\ w_{Nnom} &= 10.8 \text{ mm} \end{aligned}$$

Optimization requires
 “Low computational cost” model
 based on accurate CADENCE simulations,
 mapping the whole design space



Svikovic, V.; Cortes, J. ; Alou, P. ; Oliver, J. ; Cobos, J.A. ; Maderbacher, G. ; Sandner, C.
 “Energy-Based switches losses model for the optimization of PwrSoC buck converter”, COMPEL 2014

Turn-Off Transient Energy of PMOS



$$f_{SW} = 10 \text{ MHz}$$

$$P_{\text{TurnOFF}} = 7.86 \text{ mW}$$

$$P_{\text{TurnON}} = 1.6 \text{ mW}$$

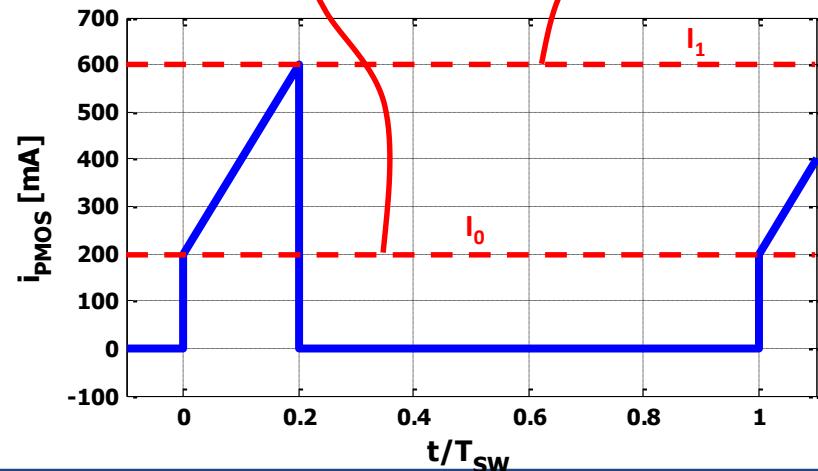
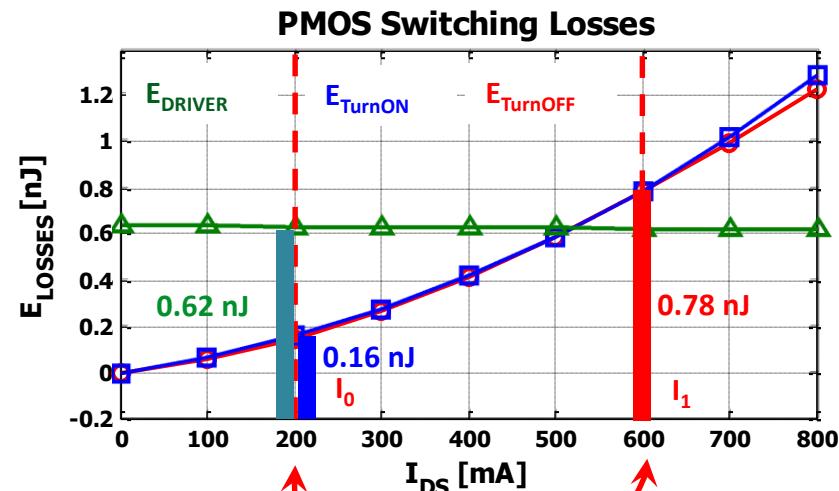
$$P_{\text{Driver}} = 6.25 \text{ mW}$$

$$I_{\text{PMOSrms}} = 186.2 \text{ mA}$$

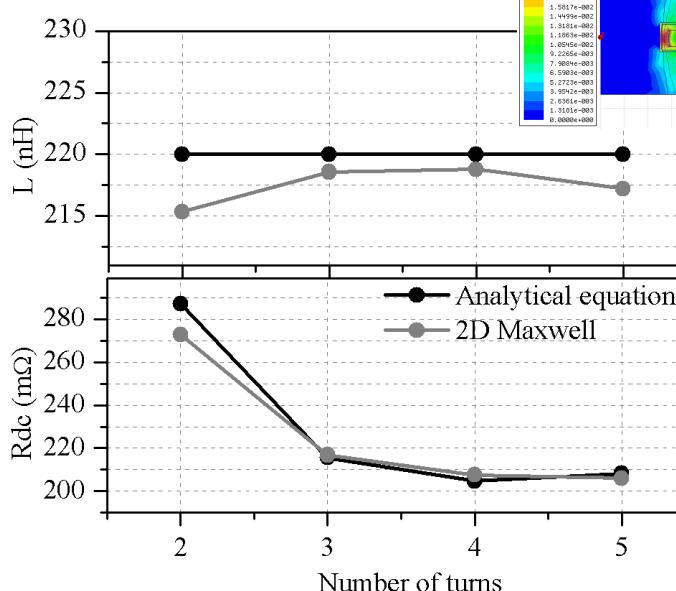
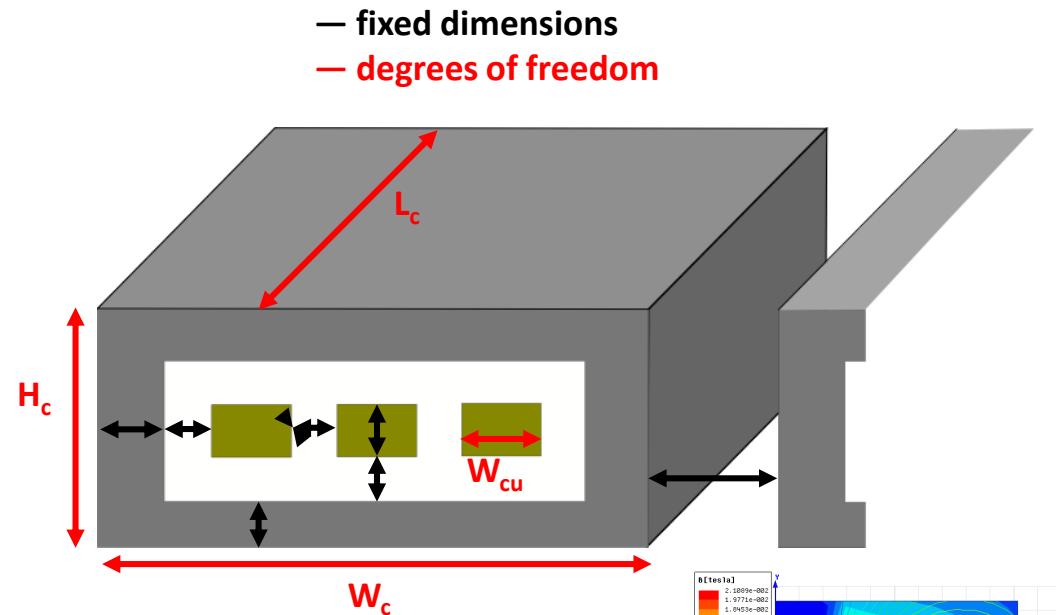
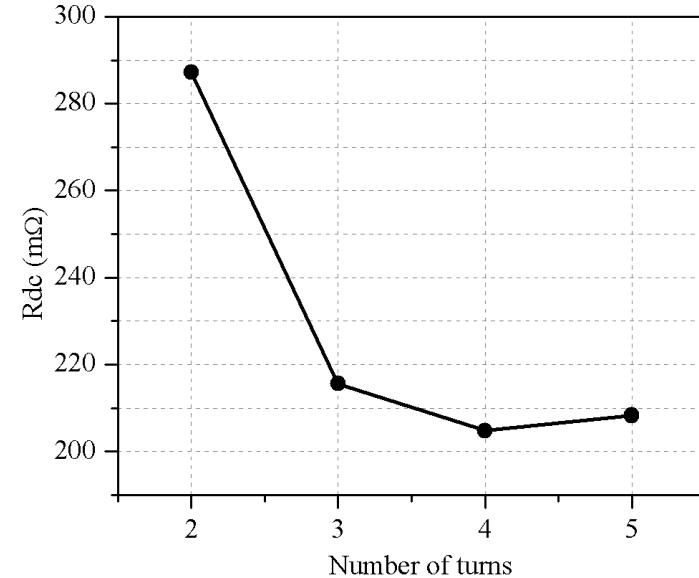
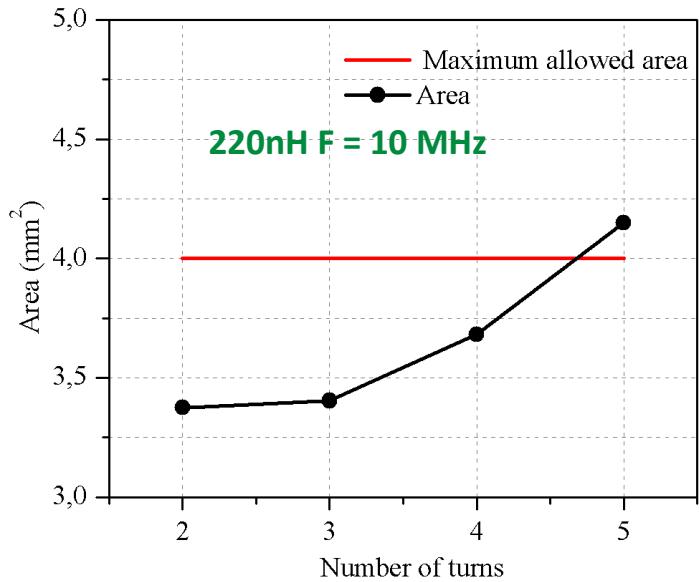
$$R_{\text{PMOSon}} = 410 \text{ m}\Omega$$

$$P_{\text{COND}} = 14.2 \text{ mW}$$

Circuit waveform to quickly calculate losses in the optimization algorithm



Inductor Optimization



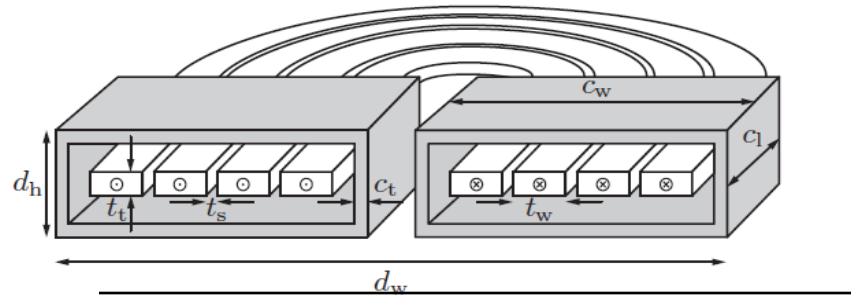
Racetrack inductor

Geometry design

- Core inductance
- Self inductance of wires

Losses calculation

- Copper losses
- Hysteresis losses
- Eddy current losses



Symbol	Description
N	Number of turns
t_w	Winding width
c_t	Winding thickness
c_s	Winding spacing
c_w	Core width
c_t	Core thickness
c_l	Core length
d_h	Device height
d_w	Device width
d_l	Device length

T.M. Andersen, C.M. Zingerli, F. Krismer, J.W. Kolar, Ningning Wang and C.O. Mathuna, "Modeling and Pareto Optimization of Microfabricated Inductors for Power Supply on Chip," Power Electronics, IEEE Transactions on , vol.28, no.9, pp.4422,4430, Sept. 2013



Geometry design

Geometry design

Core inductance

Self inductance of wires

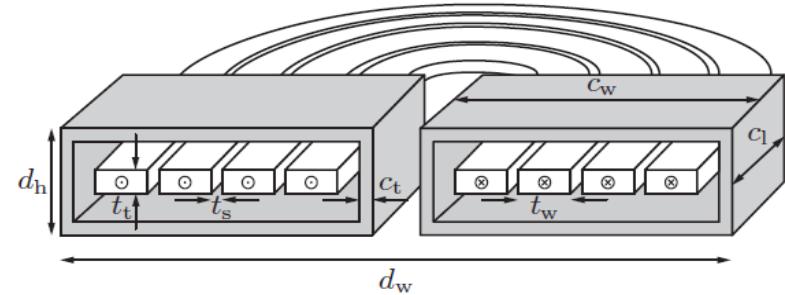
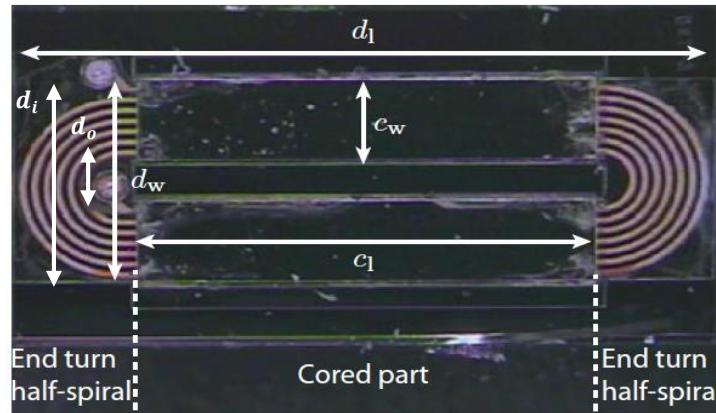
Core inductance

$$L_{core} = 2 \frac{\mu_0 \mu_c N^2 A_c}{l_m} = \frac{\mu_0 \mu_c N^2 c_t c_l}{c_w + d_h}$$

Self-inductance of wires

$$L_{t,self} \approx 0.2 c_l \left[\ln \left(\frac{2c_l}{t_w + t_t} \right) + \frac{1}{2} \right]$$

Inductance of core-less spirals



$$L_{t,spiral} \approx \frac{\mu_0 N^2 d_{avg}}{2} 0.2 c_l \left[\ln \left(\frac{2.46}{p} \right) + 0.2 p^2 \right]$$

Average diameter

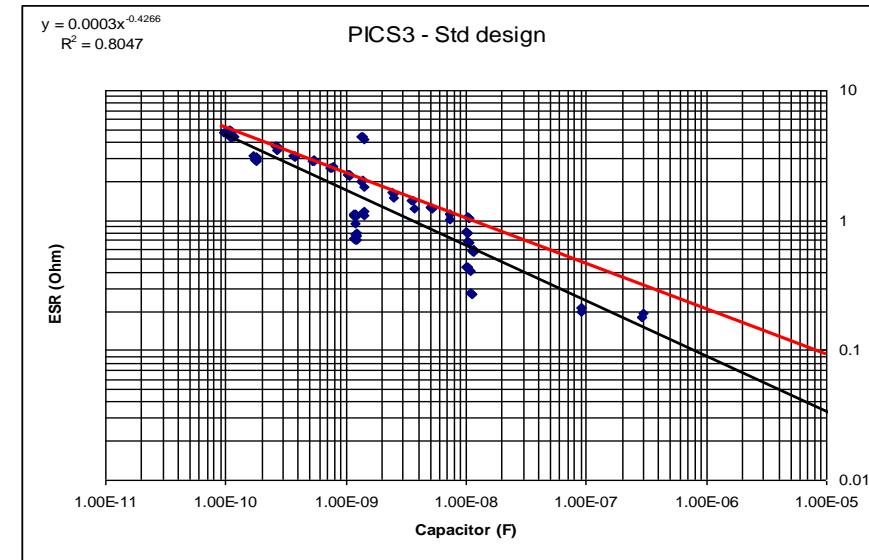
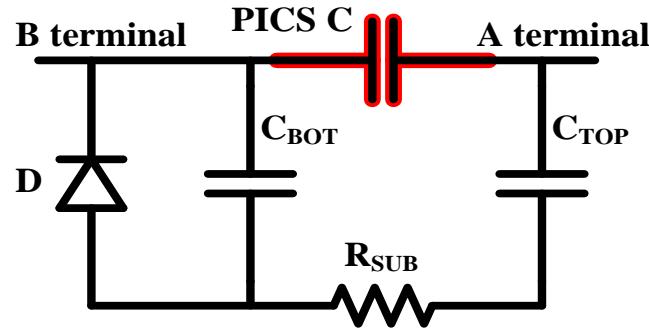
$$d_{avg} = \frac{d_o + d_i}{2}$$

Fill factor

$$p = \frac{d_o - d_i}{d_o + d_i}$$

$$L = L_{core} + L_{t,self} + L_{t,spiral}$$

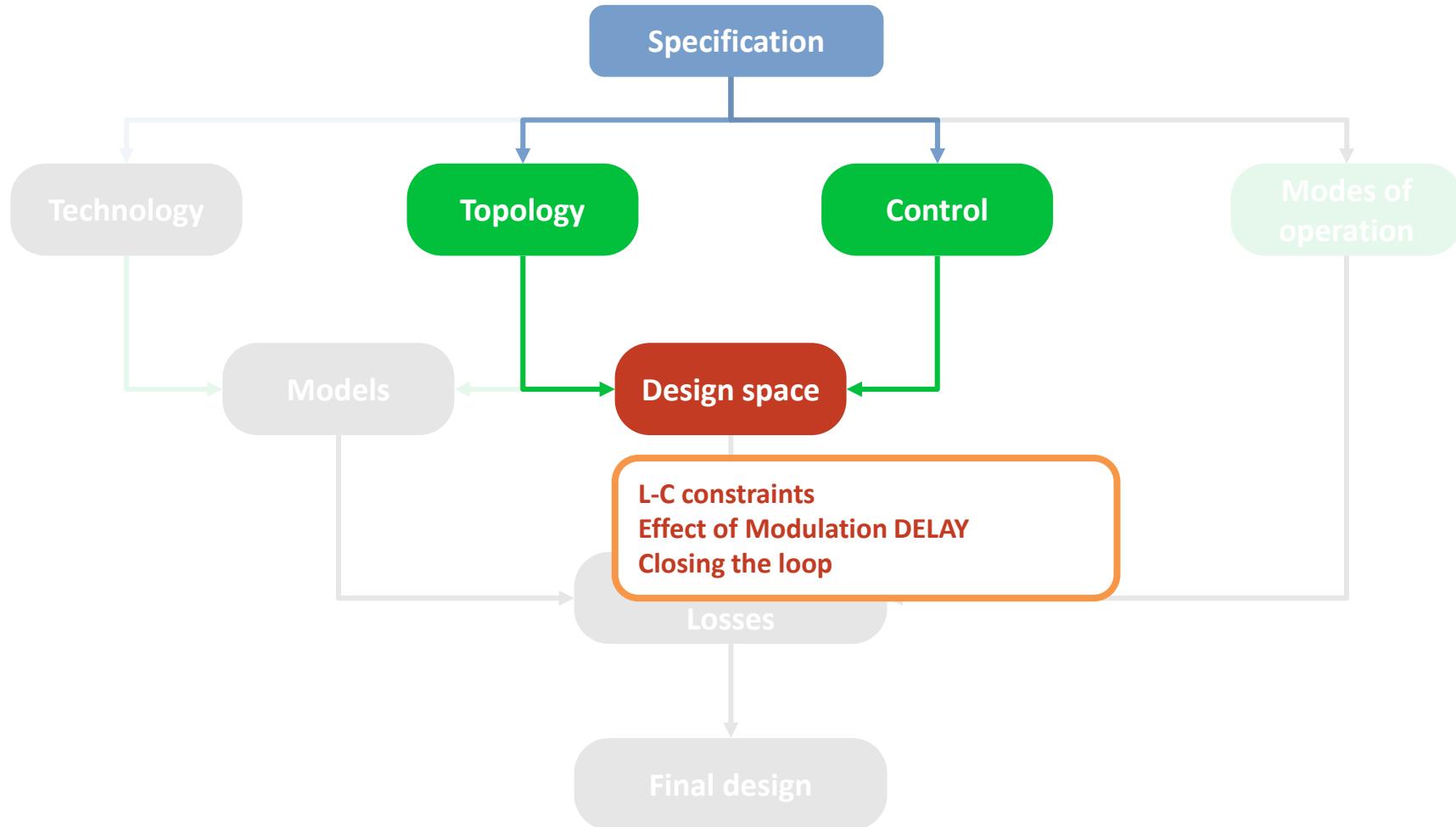
Models: Capacitors – Spice Model



	Parameters	min	typical	max
Capacitors	Pits Capacitance [nF/mm ²]	200	250	300
	Planar capacitance [nF/mm ²]	4	5.4	6.8
	Metal M1 to metal M2 [pF/mm ²]	76	80	84
	Metal M1 to substrate [pF/mm ²]	75	100	125
DIODE	Parameters			
	BV [V]	30		
	IS [A]	1.83e-16 * perimeter + 2.9e-15 * surface		
	IBVL	2 * IS		
	M	0.3		
	CJ0 [pF/mm ²]	10		
	EG [eV]	1.11		

Defined by





Design space: constraints

BUCK CONVERTER



Design decisions:

Output capacitor

Inductor filter

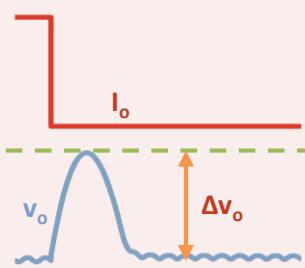
Switching frequency

Control

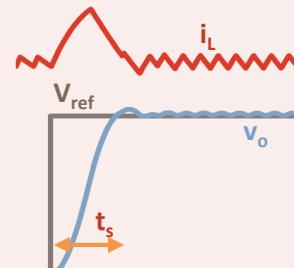
Single-phase / Multi-phase

Constraints

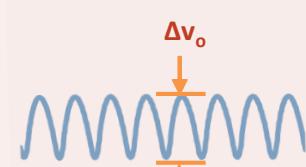
Load transients



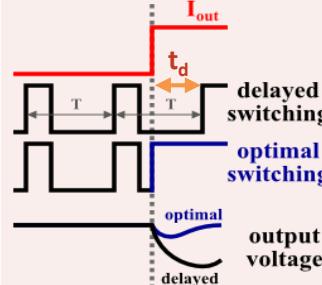
Voltage reference tracking



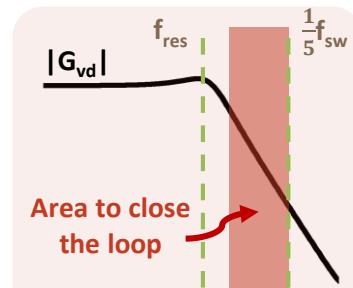
Static ripple



Modulation delays



Filter resonance in Voltage mode



$$\Delta v_o \sim cte \cdot \frac{L}{C}$$

$$t_s \sim cte \cdot \sqrt{LC}$$

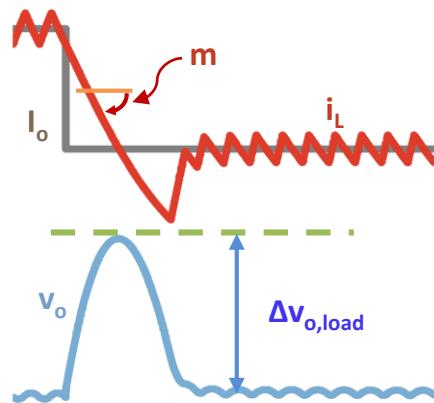
$$\Delta v_o \sim cte \cdot \frac{1}{f_{sw}} \cdot \frac{1}{LC}$$

$$t_d \sim cte \cdot \frac{1}{f_{sw}}$$

$$f_{res} \sim cte \cdot f_{sw} \cdot \frac{1}{\sqrt{LC}}$$

Design space: load transient

Load transients



$$\Delta v_{o,load}^{min} = \frac{1}{2C} \left((C \cdot ESR)^2 m + \frac{\Delta I_o^2}{m} \right)$$

Loading $m = \frac{V_{in} - v_o}{L}$

Unloading $m = \frac{v_o}{L}$

Constraints

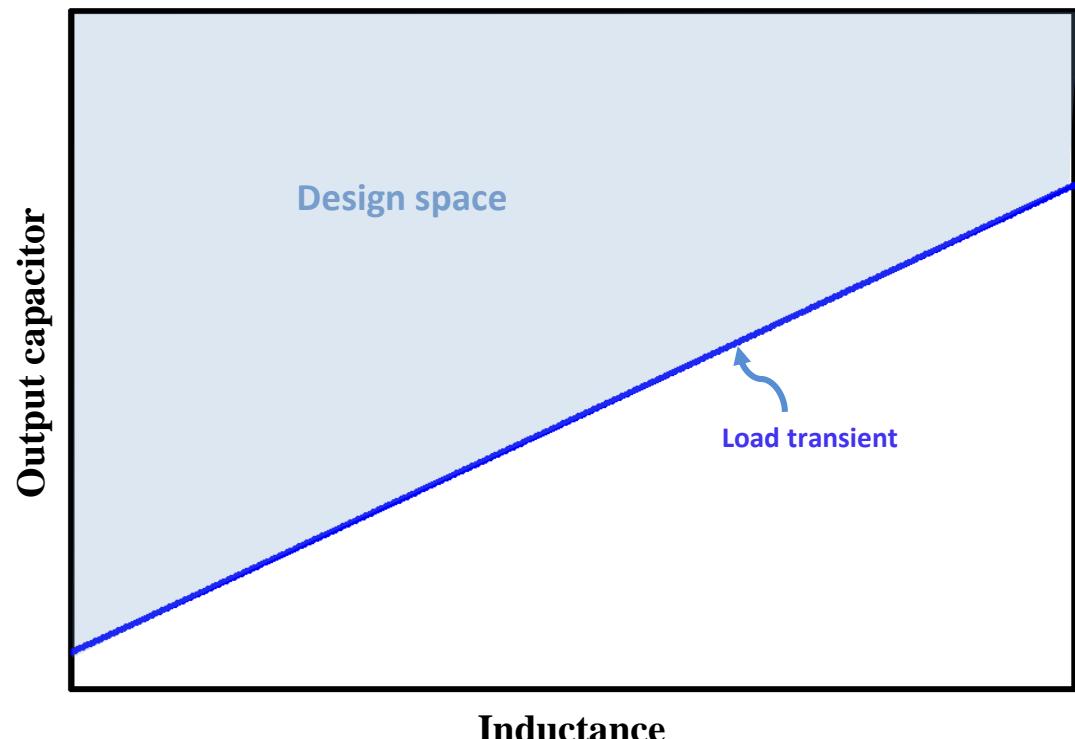
Voltage reference tracking

Static ripple

Modulation delays

Filter resonance in Voltage mode

$$\Delta v_{o,load} \sim cte \cdot \frac{L}{C}$$



Design space: voltage reference tracking

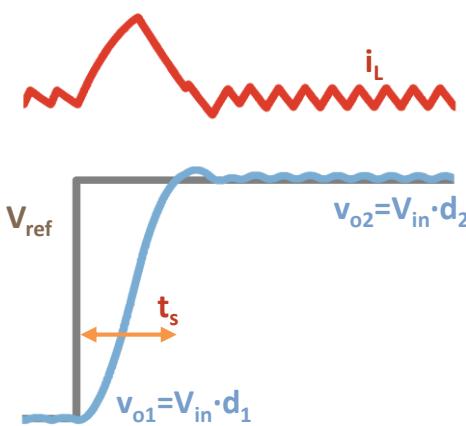
Constraints

Load transients

**Voltage reference
tracking**

Static ripple

Modulation delays

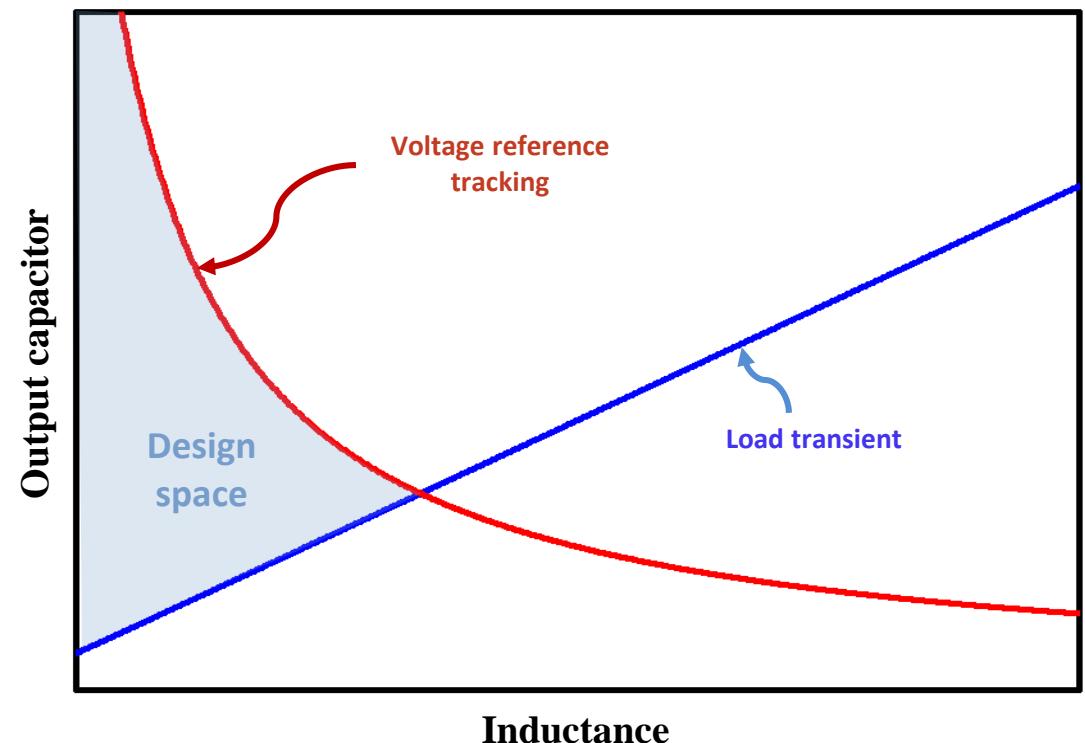
Filter resonance in
Voltage mode

$$t_s^{min} = \sqrt{\frac{2 \cdot L \cdot C}{d_m(1 - d_m) \left(\frac{1}{\Delta d} + \frac{1}{2} \right)}}$$

$$d_m = \frac{d_1 + d_2}{2}$$

$$\Delta d = |d_2 - d_1|$$

$$t_s \sim cte \cdot \sqrt{LC}$$



Design space: static ripple

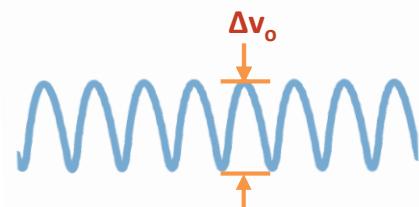
Constraints

Load transients

Voltage reference tracking

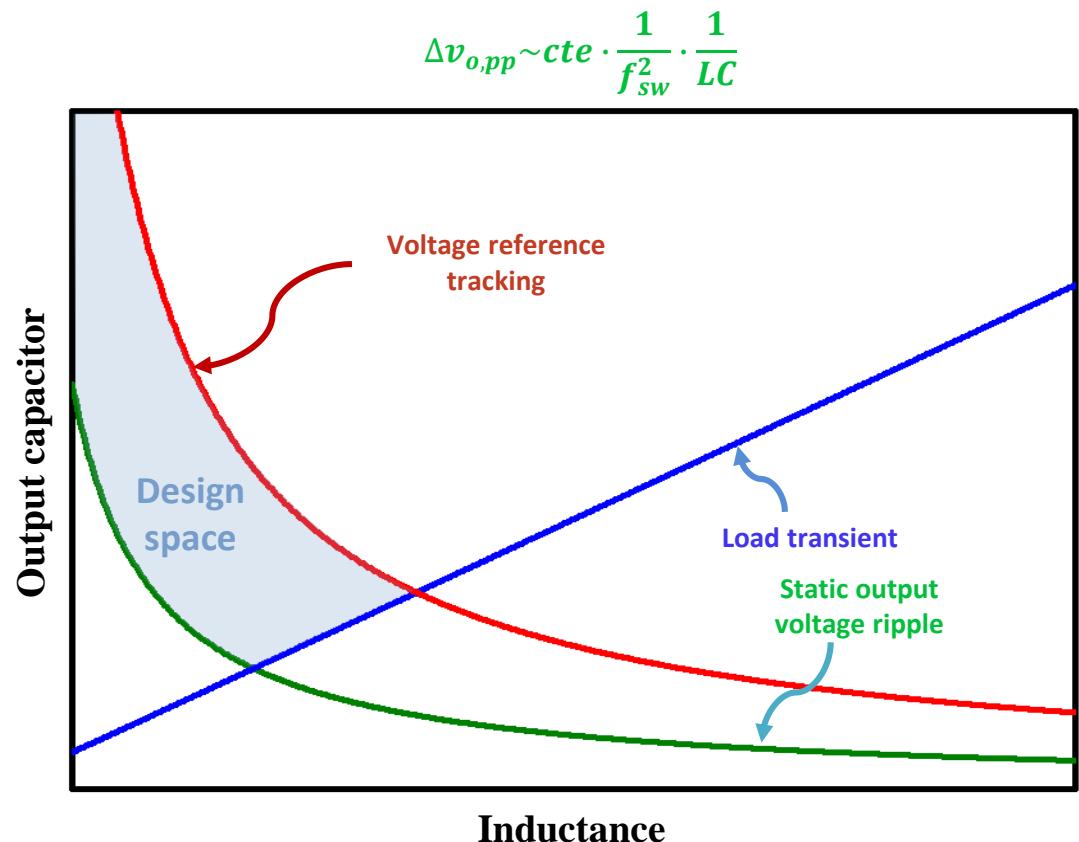
Static ripple

Modulation delays

Filter resonance in
Voltage mode

$$\Delta v_{o,pp}^{\min} \approx \Delta i_L \left(\frac{1}{8Cf_{sw}} + ESR \right)$$

$$\Delta i_L = \frac{V_{in} - v_o}{L} \frac{d}{f_{sw}}$$



Design space: static ripple

Constraints

Load transients

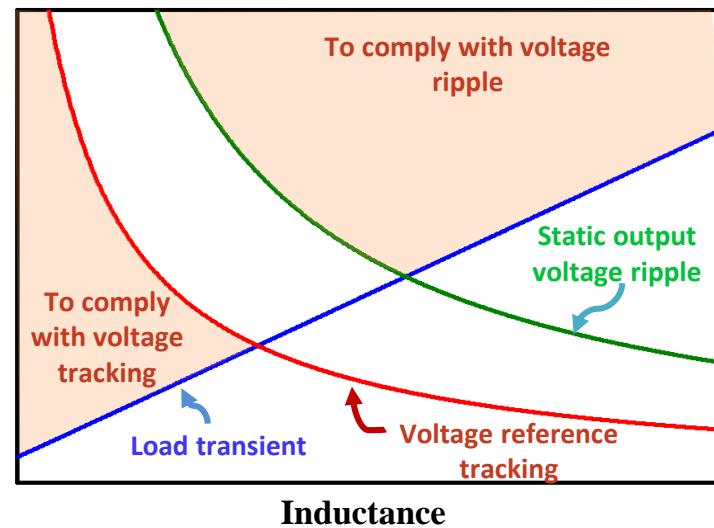
Voltage reference tracking

Static ripple

Modulation delays

Filter resonance in
Voltage mode

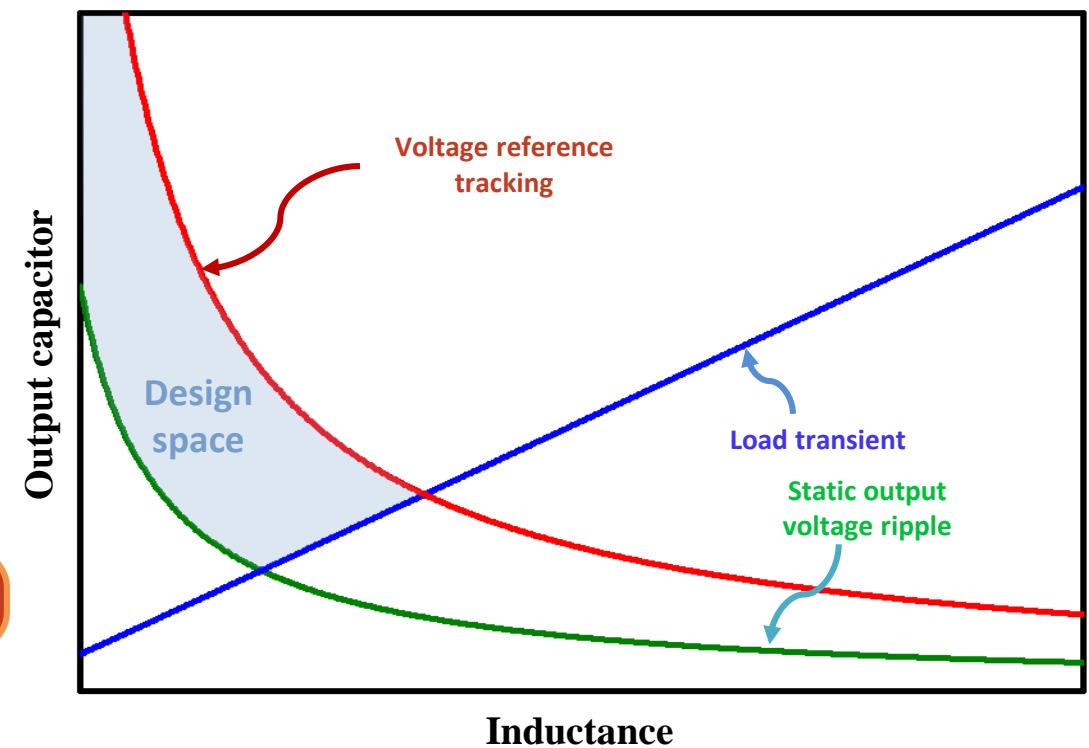
What if there is no solution
in the design space??

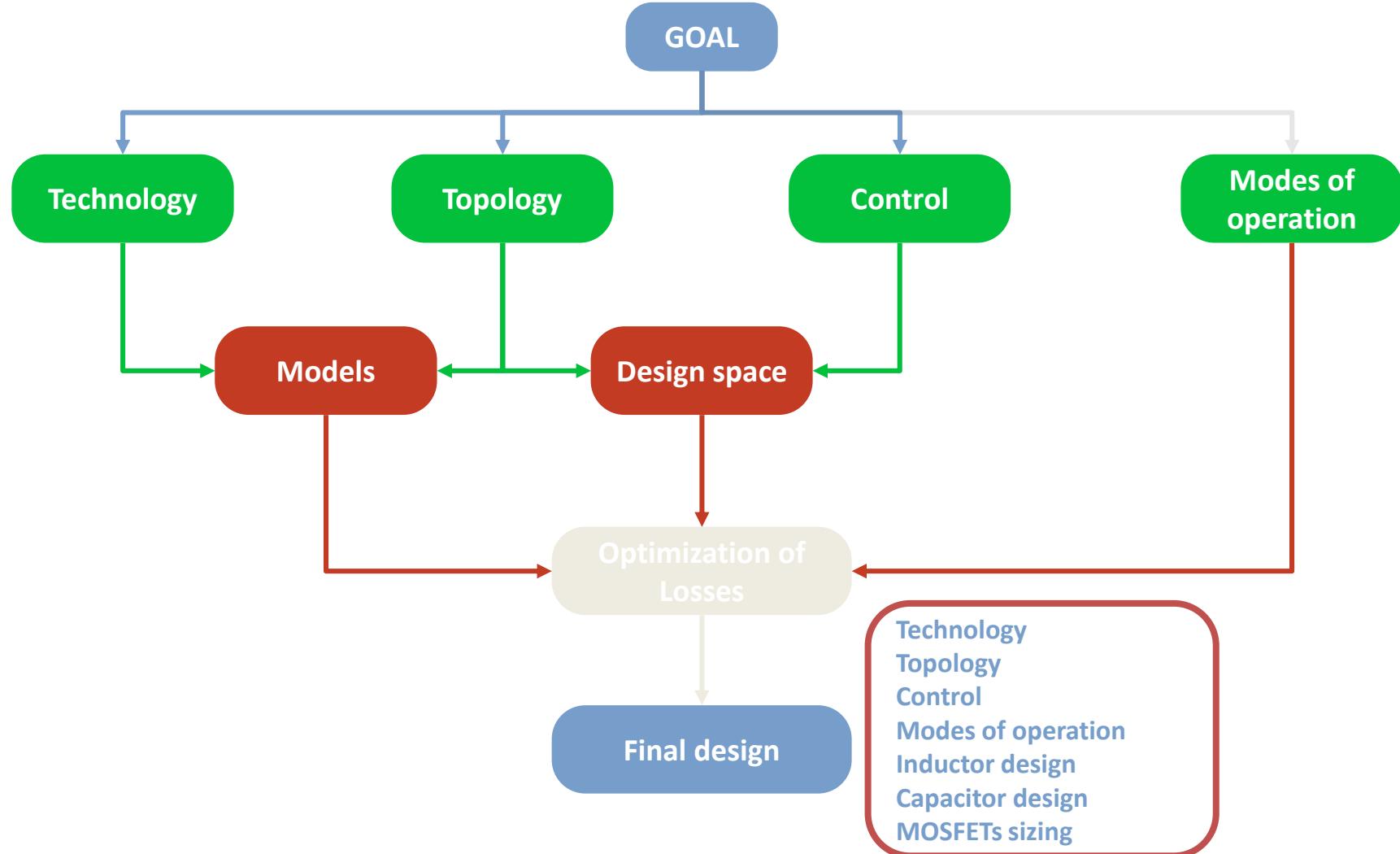


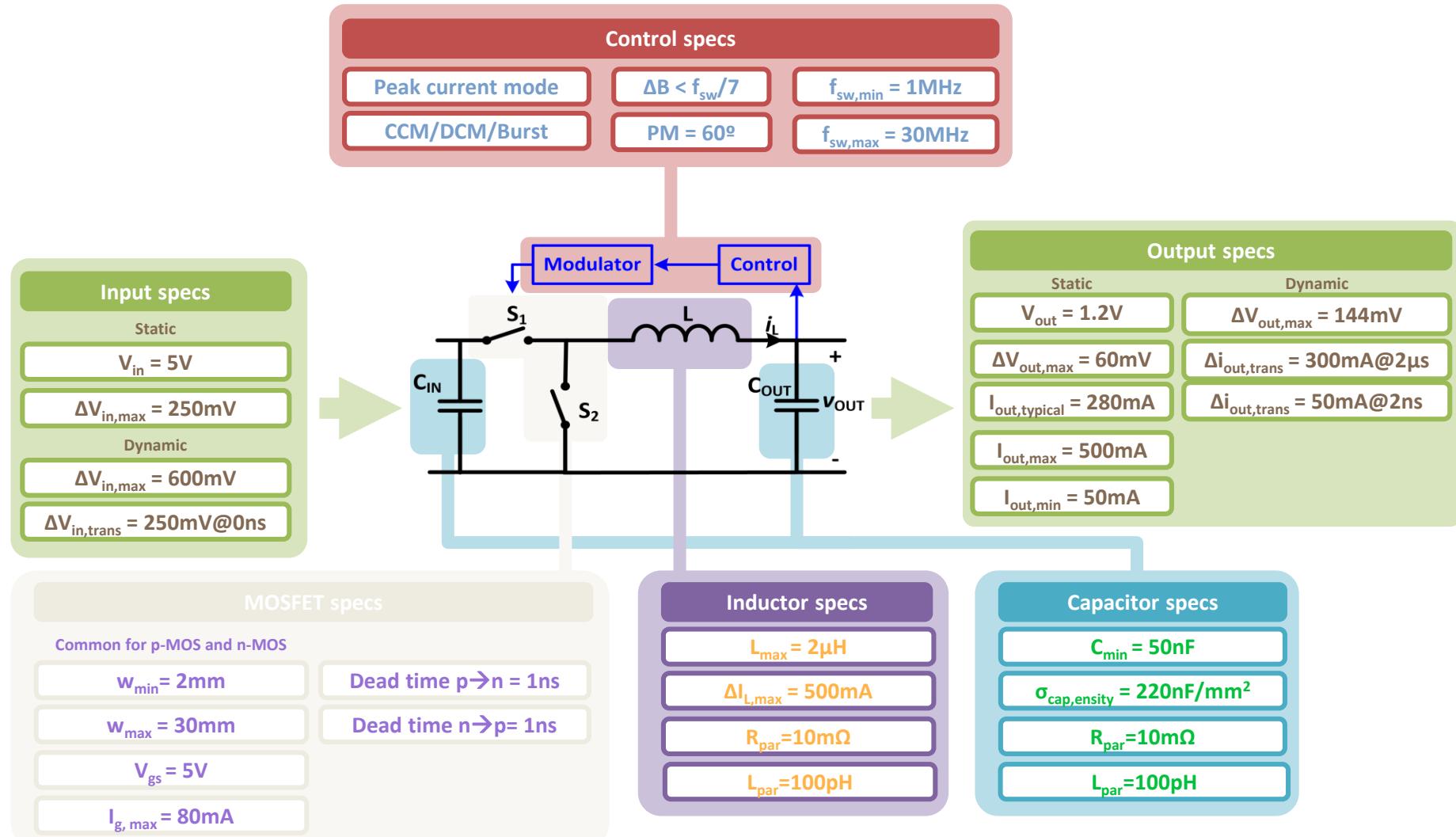
The solution is to decrease output voltage ripple by other means

Use multi-phase topology

Increase switching frequency







Capacitors

Static Spec

5 V	Infineon PG-SSOP-14	1.2V
		280mA

Regulator Constraints

Load Design

Topology

Inductor

Semiconductors

Total Area

Optimization

Cin/Cout **Lout** **fsw**

wp **wn** **Area**

Results of the optimization process

175 nF / 245 nF	201 nH	11.7 MHz
12 mm	14.1 mm	9.9 mm ²

Operating Mode

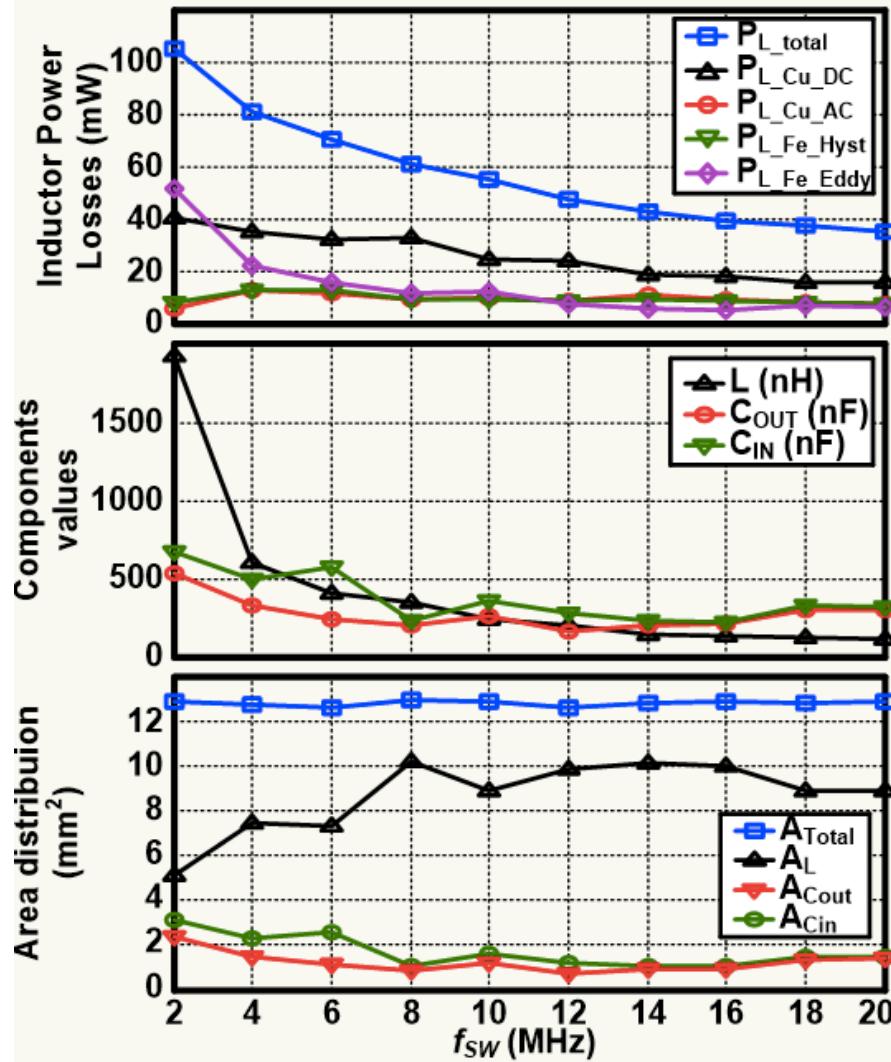
- continuous Conduction Mode
- continuous Conduction Mode
- BURST Mode

Analysis of the system

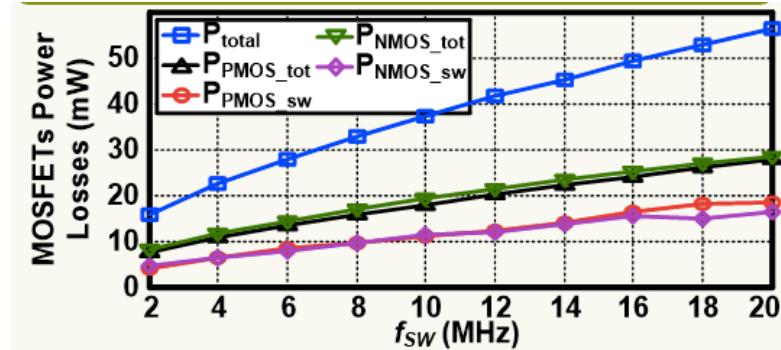
PAGE 42

Results (& “what if” analysis)

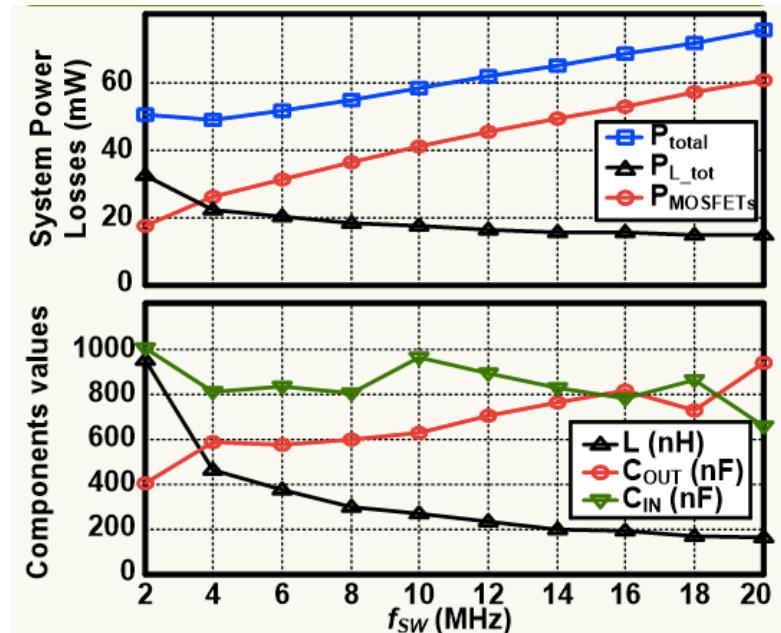
Ideal MOSFETs – Real Inductor



Real MOSFETs – Ideal Inductor

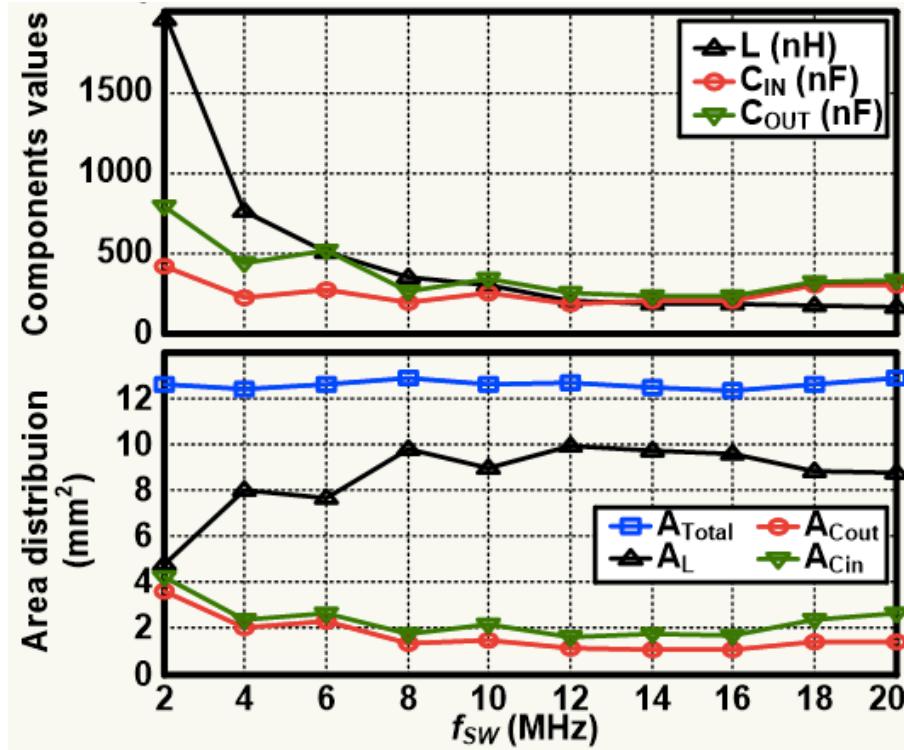
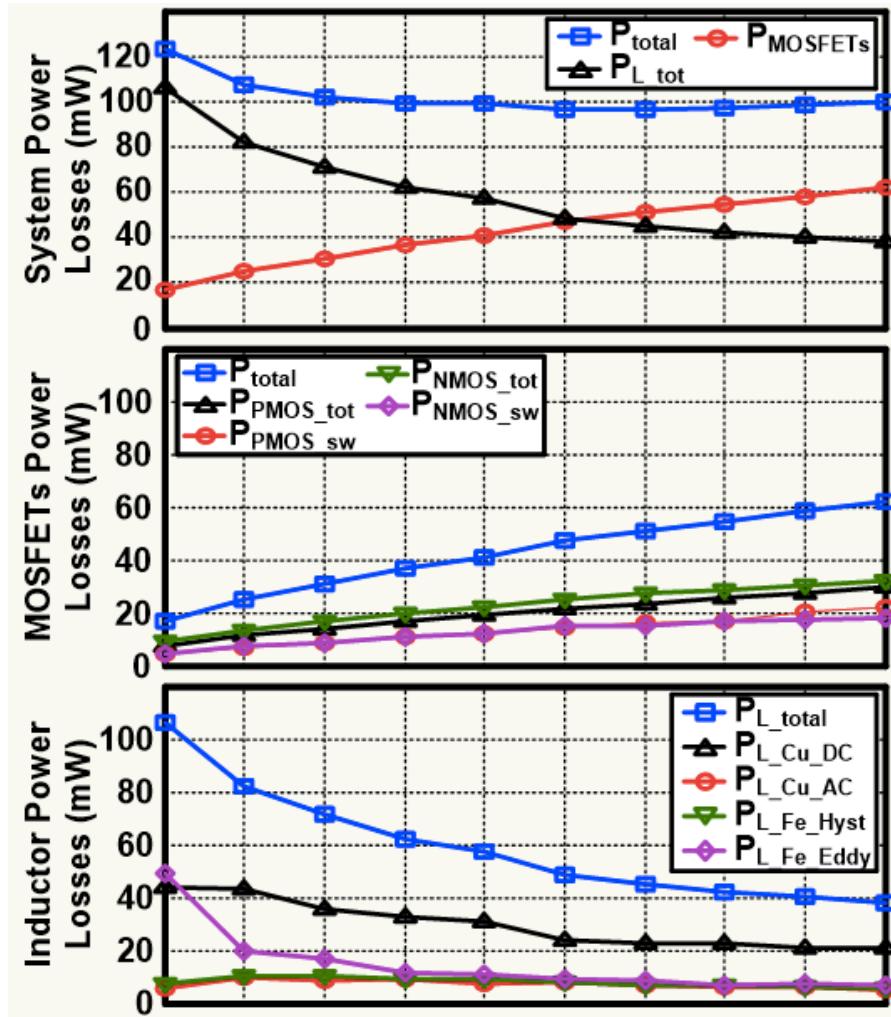


Real MOSFETs – Inductor with Cu losses



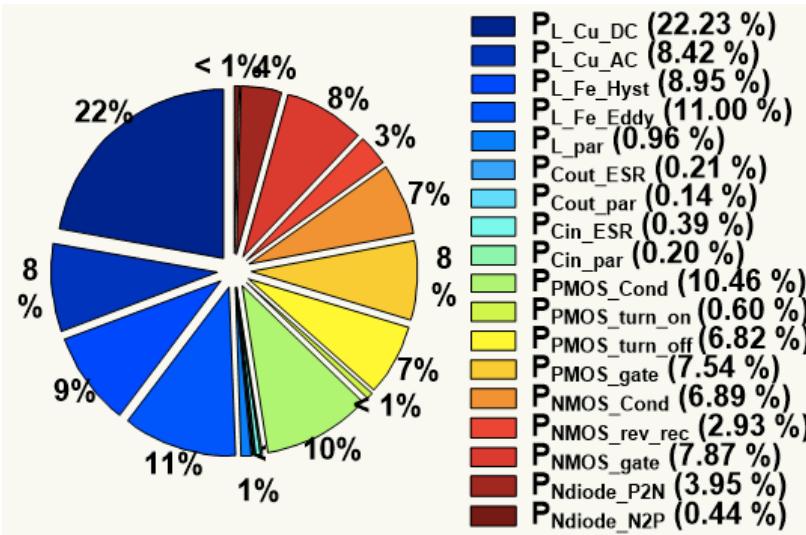
Results (& “what if” analysis)

Real MOSFETs – Real Inductor

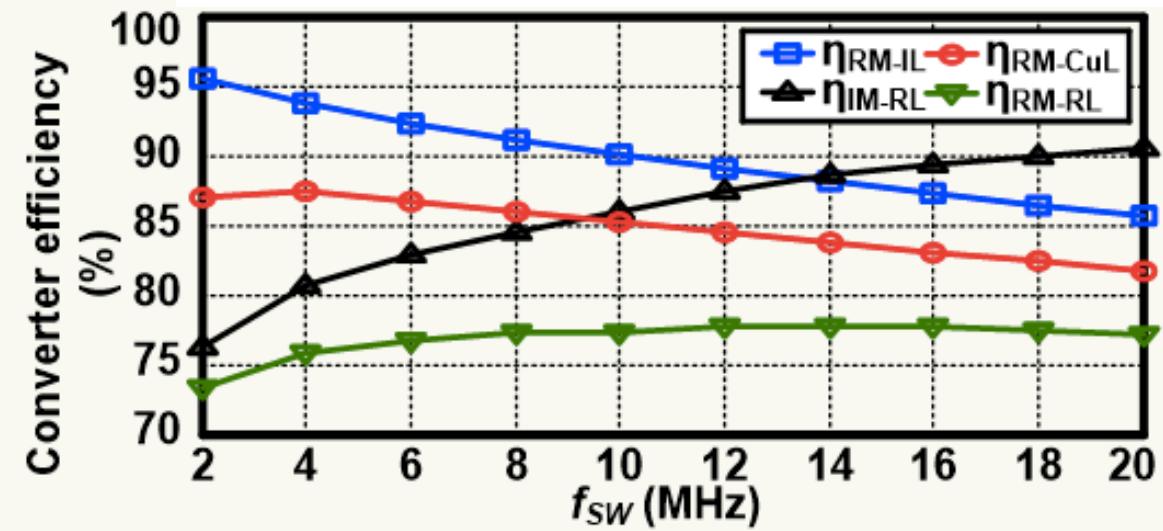


Results (& “what if” analysis)

Optimal solution: Losses Breakdown

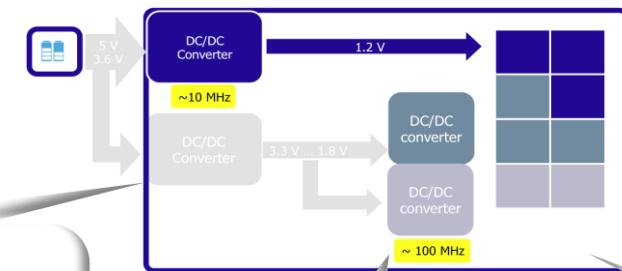
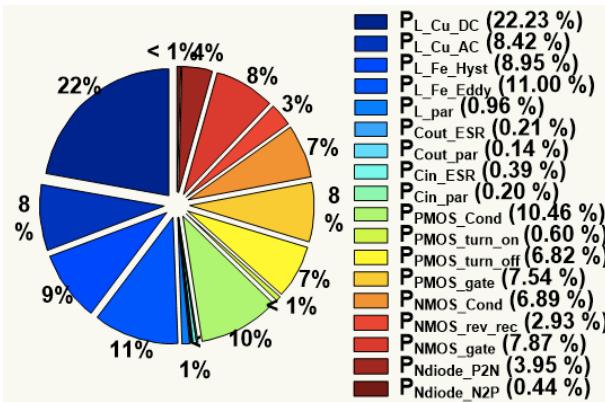


Converter efficiency comparison



Technology impact:

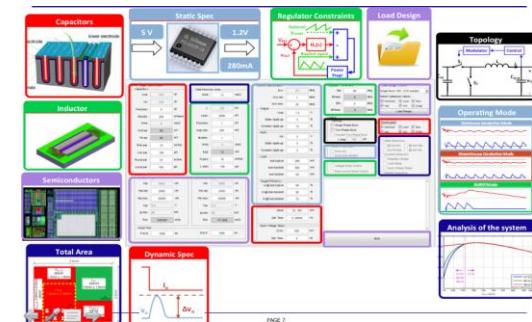
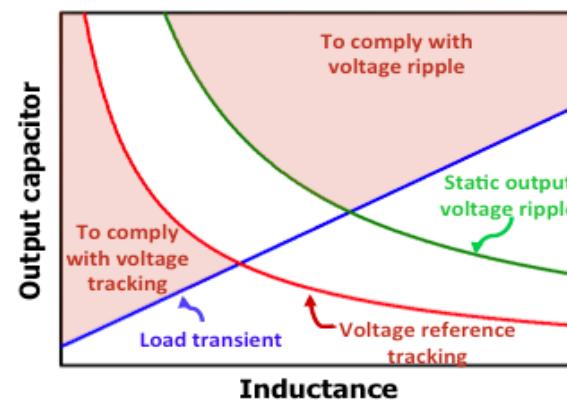
- CMOS improvement: optimum $f_{sw} \uparrow$
- Inductor technology improvement: optimum $f_{sw} \downarrow$



Models, algorithms and tools to OPTIMIZE your design

Calculate the “**Design space**” for your specs:

- Load steps
- Voltage or reference steps
- V_{out} ripple
- Multi-phase, modulation delays, ...



Thank you for your attention!

- **PowerSwipe Partners:**
 - Tyndall National Institute / University College Cork, Ireland
 - Infineon Technologies AG, Germany
 - Infineon Technologies Austria AG, Austria
 - IPDiA, France
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- **This work is funded by:**
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